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**(54) METHOD FOR TRANSFERRING MICRO-LEDS AND METHOD FOR MANUFACTURING MICRO-LED DEVICE**

VERFAHREN ZUR ÜBERTRAGUNG VON MIKRO-LEUCHTDIODEN UND  
HERSTELLUNGSVERFAHREN FÜR MIKRO-LEUCHTDIODENBAUELEMENT

PROCÉDÉ DE TRANSFERT DE MICRO-DIODES ÉLECTROLUMENESCENTES ET PROCÉDÉ DE  
FABRICATION D'UN DISPOSITIF À MICRO-DIODES ÉLECTROLUMENESCENTES

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## Description

### FIELD OF THE INVENTION

[0001] The present invention relates to a method for transferring micro-LEDs at wafer level and a method for manufacturing a micro-LED device.

### BACKGROUND OF THE INVENTION

[0002] The micro-LED technology refers to the LED array of small size integrated on a substrate with high density. Currently, the micro-LED technology is starting development, and it is expected in the industry that a high-quality micro-LED product comes into the market. High-quality micro-LED will have a deep affection on the conventional display products such as LCD/OLED that have already been put into the market.

[0003] In the process of manufacturing micro-LEDs, micro-LEDs are first formed on a donor wafer, and then the micro-LEDs are transferred to a receiving substrate. The receiving substrate is a display screen, for example.

[0004] One difficulty during manufacturing a micro-LED lies in how to transfer a micro-LED from a donor wafer to a receiving substrate. In the prior art, the transfer is generally performed by means of electrostatic pick-up. A transfer head array will be needed during the electrostatic pick-up. The structure of the transfer head array is relatively complicated, and the stability thereof shall be considered. An extra cost shall be paid for manufacturing a transfer head array. A phase change shall be made before pick-up with the transfer head array. In addition, during manufacturing with a transfer head array, limitations apply to the thermo budget of a micro-LED for phase change, which is generally lower than 350°C, or more specifically, lower than 200°C; otherwise, the performance of the micro-LED will be degraded. It generally requires two transfers during the manufacturing with transfer head array, i.e., the transfer from a donor wafer to a carrier wafer and the transfer from the carrier wafer to a receiving substrate.

[0005] US patent No. 8,333,860B1 discloses an array of transfer heads for transferring micro devices, in which a voltage is applied to the electrode in the transfer head to pick-up a micro device.

[0006] US patent No. 8,426,227B1 discloses a method of forming a micro light emitting diode array, in which a micro-LED array is transferred to a receiving substrate by using a transfer head array.

[0007] Patent Applications US 2014/0159065 A1, US 2010/0259164 A1 and US 2011/0151602 A1 disclose other methods of manufacturing a micro-LED device by transferring selected micro-LEDs onto a receiving substrate.

### SUMMARY OF THE INVENTION

[0008] One object of this invention is to provide a new

technical solution for transferring micro-LED at wafer level.

[0009] The present invention provides a method for transferring micro-LEDs at wafer level according to claim 1.

[0010] Preferably, the micro-LEDs are vertically-structured micro-LEDs, and the method further comprises: forming N electrodes on the micro-LEDs on the receiving substrate; and performing encapsulation on the N electrodes.

[0011] Preferably, the first bonding layer is a UV or light releasable tape.

[0012] Preferably, the carrier substrate is a PET plate.

[0013] Preferably, the partial release and the full release are performed by light exposure.

[0014] Preferably, the second bonding layer is released by thermal release.

[0015] Preferably, the selected micro-LEDs are arranged on the receiving substrate in a redundant manner.

[0016] Preferably, a contactless force is applied onto the micro-LEDs during the partial release.

[0017] Preferably, the contactless force is at least one of gravity, electrostatic force and electromagnetic force.

[0018] The present invention also provides a method for manufacturing a micro-LED device according to claim 10.

[0019] In addition, it should be understood by a person skilled in the art that, although a lot of problems exist in the prior art, the solution of each embodiment of the present invention could just improve in one or several aspects, and it is not necessary for it to solve all the technical problems listed in the Background of the Invention or in the prior art.

[0020] Further features of the present invention and advantages thereof will become apparent from the following detailed description of exemplary embodiments of the present invention with reference to the attached drawings.

### BRIEF DESCRIPTION OF THE DRAWINGS

[0021] The accompanying drawings, which constitute a part of the specification, illustrate embodiments of the present invention and, together with the description thereof, serve to explain the principles of the present invention.

Figure 1 shows a flow chart of an example not forming part of the present invention.

Figure 2A to 2G shows an example not forming part of the present invention.

Figure 3 shows a flow chart of another example not forming part of the present invention.

Figures 4A to 4L show another example not forming part of the present invention.

Figure 5 shows a flow chart of still another example not forming part of the present invention.

Figures 6A to 6F show an example not forming part

of the present invention.

Figures 7A to 7L show still another example not forming part of the present invention.

Figure 8 shows still another example not forming part of the present invention.

Figure 9 shows still another example not forming part of the present invention.

Figure 10 shows a flow chart of a method for transferring micro-LEDs which may be used as part of the method for transferring micro-LEDs at wafer level according to the present invention.

Figure 11 shows a flow chart of still another illustrative example not forming part of the present invention.

Figures 12A to 12F show an example for repairing micro-LED defects not forming part of the present invention.

Figure 13 shows a flow chart of still another illustrative example not forming part of the present invention.

Figures 14A to 14C show an example for pre-screening defect micro-LEDs not forming part of the present invention.

Figures 15A to 15B show another example for pre-screening defect micro-LEDs not forming part of the present invention.

Figures 16A to 16B is an enlarged view of the area "A" of Figure 15B.

Figure 17 shows a flow chart of an embodiment of the method according to the present invention.

Figures 18A to 18J show an embodiment of the method for transferring micro-LEDs at wafer level according to the present invention.

## DETAILED DESCRIPTION OF THE EMBODIMENTS

**[0022]** Various examples and embodiments of the present invention will now be described in detail with reference to the drawings. It should be noted that the relative arrangement of the components and steps, the numerical expressions, and numerical values set forth in these embodiments do not limit the scope of the present invention unless it is specifically stated otherwise.

**[0023]** The following description of at least one exemplary embodiment is merely illustrative in nature and is in no way intended to limit the invention, its application, or uses.

**[0024]** Techniques, methods and apparatus as known by one of ordinary skill in the relevant art may not be discussed in detail.

**[0025]** In all of the examples and embodiments illustrated and discussed herein, any specific values should be interpreted to be illustrative only and non-limiting.

**[0026]** Notice that similar reference numerals and letters refer to similar items in the following figures, and thus once an item is defined in one figure, it is possible that it need not be further discussed for following figures.

**[0027]** Fig. 1 shows a flow chart of an example of a

method for transfer micro-LED not forming part of the present invention.

**[0028]** As shown in Fig. 1, at step S1100, a micro-LED is formed on a laser-transparent original substrate.

5 **[0029]** The laser-transparent original substrate can be a sapphire substrate, SiC substrate and so on, for example. The micro-LED can be used for being mounted on a display screen panel.

10 **[0030]** It should be understood by a person skilled in the art that one micro-LED could be formed on the original substrate, or a plurality of micro-LED could be formed on the original substrate. For example, a plurality of micro-LEDs can be formed on the laser-transparent original substrate. The plurality of micro-LEDs can form an array.

15 **[0031]** In an example, in a case where a plurality of micro-LEDs are formed on the laser-transparent original substrate, the original substrate can be singulated or divided into multiple pieces for more flexible transferring.

20 **[0032]** At step S 1200, the micro-LED is brought into contact with a pad preset on a receiving substrate.

**[0033]** For example, the receiving substrate is a display screen panel.

**[0034]** For example, the pad can be set for red pixel array, yellow pixel array or blue pixel array.

25 **[0035]** In an example, in a case where a plurality of micro-LED are formed, at least one micro-LED of the plurality of micro-LEDs can be brought into contact with at least one pad preset on the receiving substrate. The at least one micro-LED could be one, several or all of the plurality of micro-LEDs. It should be understood by a person skilled in the art that, although it is just described here that at least one micro-LED, which is expected to be lifted-off, is in contact with a pad, a remaining micro-LED of the plurality of micro-LEDs can also be in contact with a pad.

30 **[0036]** For example, in the step of contact (S 1200), the micro-LED can be brought into contact with the pad preset on the receiving substrate via a liquid thin film. For example, the liquid thin film can include flux. Herein, the lift-off of a micro-LED will be easy through the surface tension force of the liquid thin film (flux), and the successful rate is high.

35 **[0037]** At step S1300, the original substrate is irradiated with laser from the original substrate side to lift-off the micro-LED from the original substrate.

40 **[0038]** In an example, in a case where at least one micro-LED is in contact with pad, at least one area on the original substrate can be irradiated with laser from the original substrate side to lift-off the at least one micro-LED from the original substrate. For example, a technician can select the at least one area. For example, the at least one area corresponds to the at least micro-LED, respectively. The at least one area can be just partial area on the original substrate, or can be the whole area.

45 **[0039]** In another example, the original substrate can be offset for transferring additional micro-LED s.

**[0040]** In another example, after the transferring using the original substrate, an additional laser-transparent

backup substrate can be used to cope with a situation in which micro-LEDs are missing at some points on the display screen panel. For example, a micro-LED can be formed on an additional laser-transparent backup substrate; the micro-LED on the backup substrate is brought into contact with a pad preset on a receiving substrate; and the backup substrate is irradiated with laser from the backup substrate side to lift-off the micro-LED from the backup substrate. In such a way, the quality of a display screen can further be improved.

**[0041]** An array of micro-LEDs can be formed on the receiving substrate after the transferring of micro-LEDs to the receiving substrate.

**[0042]** After the transferring of micro-LEDs to the receiving substrate, the present invention can further include subsequent steps.

**[0043]** For example, the lifted-off micro-LEDs can be reflow-soldered on the receiving substrate. A negative electrode can be deposited on the micro-LEDs. The reflow-soldering can be performed after micro-LEDs of each color are transferred. Alternatively, the reflow-soldering can be performed after micro-LEDs of all colors are transferred.

**[0044]** In addition, the soldered micro-LED can be filled with polymer. For example, a confocal dielectric deposition can be used in stead of polymer filling.

**[0045]** In comparison with the prior art, under the similar conditions, the micro-LED manufactured by using the method of the present invention is relatively simple and reliable while maintaining a high quality, and the throughput thereof is relatively high with low cost.

**[0046]** In accordance with the present invention, a micro-LED is formed directly on the original substrate and it is transferred to a receiving substrate by means of laser lift-off.

**[0047]** An example for transferring a micro-LED not forming part of the present invention will be described below with reference to Figs. 2A to 2G.

**[0048]** As shown in Fig. 2A, micro-LEDs 2 are formed on a laser-transparent original substrate 1 such as sapphire substrate. The micro-LEDs 2 have a vertical micro-LED structure, for example. The micro-LEDs 2 contains, for example, a n-doped GaN layer, a multiple quantum well structure, a p-doped GaN layer, a p metal electrode, a bump, and so on.

**[0049]** As shown in Fig. 2A, the plurality of micro-LEDs 2 can be singulated.

**[0050]** As shown in Fig. 2B, the original substrate 1 is flipped over, and is aligned with a receiving substrate 4 with liquid thin film (for example, containing flux) 5. The micro bumps on the micro-LEDs are in contact with the flux. Pads 3 are preset on the receiving substrate 4. For example, the pads 3 include pad 3r for receiving red micro-LED, pad 3b for receiving blue micro-LED and pad 3g for receiving green micro-LED.

**[0051]** As shown in Fig. 2C, partial areas 7 on the original substrate are selectively irradiated with laser 7, to lift off the selected micro-LEDs 2a, 2b of the plurality of

formed micro-LEDs from the original substrate.

**[0052]** As shown in Fig. 2D, the original substrate 1 is lifted up. Because of the function of the surface tension force of the liquid thin film, the selected micro-LEDs 2a, 2b are lifted-off easily, while the other micro-LEDs are remained on the original substrate 1.

**[0053]** Then, the original substrate is moved and the operations of Figs. 2C to 2D are repeated, so that a plurality of micro-LEDs are transferred to the receiving substrate.

**[0054]** As shown in Fig. 2E, the plurality of micro-LEDs are transferred to the receiving substrate 4.

**[0055]** As shown in Fig. 2F, for example, the plurality of micro-LEDs are soldered onto the receiving substrate through reflow soldering. Then, the flux is cleaned.

**[0056]** As shown in Fig. 2G, the receiving substrate is filled with polymer 8 and is sealed. Then, n-metal electrode 9 is deposited, for example, using ITO material.

**[0057]** Figure 3 shows a flow chart of another example of a method for transferring a micro-LED not forming part of the present invention.

**[0058]** As shown in Figure 3, at step S2100, micro-LEDs are formed on a laser-transparent original substrate.

**[0059]** At step S2200, an anisotropic conductive layer is provided on a receiving substrate.

**[0060]** For example, the anisotropic conductive layer is at least one of an anisotropic conductive film (ACF), an anisotropic conductive paste (ACP) and an anisotropic conductive tape (ACT).

**[0061]** At step S2300, the micro-LEDs are brought into contact with the anisotropic conductive layer on the receiving substrate. For example, the micro-LEDs are adhered to the anisotropic conductive layer on the receiving substrate. At this step, the micro-LEDs can be aligned with the receiving substrate in advance, for example.

**[0062]** At step S2400, the original substrate is irradiated with laser from the original substrate side to lift-off the micro-LEDs from the original substrate.

**[0063]** For example, the above steps can be performed with respect to red micro-LEDs, green micro-LEDs and blue micro-LEDs, respectively. Since the transfer with respect to the three micro-LEDs can be regarded as a simple repeat of the above steps, they are not repeated here.

**[0064]** At step S2500, the anisotropic conductive layer is processed to electrically connect the micro-LEDs (its electrodes) with the pads on the receiving substrate.

**[0065]** In an example, pressure can be applied on the anisotropic conductive layer from the micro-LED side by using an auxiliary substrate. For example, the temperature of processing the anisotropic conductive layer can be between 150°C and 200°C. For example, the applied pressure is between 1 MPa and 4 MPa. For example, the time period of applying pressure is between 10 second and 30 second.

**[0066]** In an example, the auxiliary substrate can be a flat rigid substrate. The inventors of the present applica-

tion have found that the possible displacement of the micro-LEDs can be reduced by using a rigid substrate.

**[0067]** For example, the surface of the auxiliary substrate can be coated with temporary bonding polymer. In this situation, the step S2500 can further comprises: bonding the auxiliary substrate with the anisotropic conductive layer via the temporary bonding polymer; and after applying pressure, de-bonding the auxiliary substrate via the temporary bonding polymer, to remove the auxiliary substrate. The advantage of temporarily bonding the auxiliary substrate with the anisotropic conductive layer lies in that, the positions of the micro-LEDs can be relatively fixed, and the displacement of micro-LEDs during processing the anisotropic conductive layer is reduced.

**[0068]** After the above processes, normal subsequent processes can be done on the micro-LEDs. For example, the subsequent processes include: etching the temporary bonding polymer, to expose the epitaxial layers of the micro-LEDs; forming N-metal electrodes on the epitaxial layers of the micro-LEDs; and performing encapsulation on the N-metal electrodes.

**[0069]** For example, the receiving substrate can be a display substrate. Leads and pads can be set on the receiving substrate in advance, to be electronically connect with the micro-LEDs.

**[0070]** In this example, the micro-LEDs and the receiving substrate are connected through a anisotropic conductive layer. This approach of processing is relatively simple and is more suitable for production in large bulk.

**[0071]** For example, the receiving substrate is a display screen or display substrate. The micro-LED device is a display device, for example.

**[0072]** Figure 4A to 4L shows another example for transferring a micro-LED not forming part of the present invention.

**[0073]** As shown in Figure 4A, an original substrate 201 such as a sapphire substrate has red micro-LEDs 202 thereon. The receiving substrate 204 such as display substrate has an anisotropic conductive film (ACF) 203 thereon. The receiving substrate 204 has signal leads 205 and pads 205' for connecting micro-LEDs.

**[0074]** As shown in Figure 4B, the original substrate 201 (red micro-LED 202) is brought into contact with the anisotropic conductive film 203 with a light force. For example, the red micro-LEDs 202 to be transferred can be aligned with the pads on the receiving substrate 204. The original substrate 201 is irradiated with laser 206, to selectively lift-off red micro-LEDs.

**[0075]** Figure 4C shows lifted-off red micro-LEDs 202r.

**[0076]** Figure 4D shows an original substrate 207 and the green micro-LEDs 208 thereof. The green micro-LEDs to be lifted-off are aligned with the pads on the receiving substrate 204.

**[0077]** Figure 4E shows the situation in which the green micro-LEDs 208 are in contact with the anisotropic conductive film 203 with a light force. At least one green micro-LED is selectively lifted-off by using laser 209.

**[0078]** Figure 4F shows lifted-off red micro-LEDs 202r and green micro-LEDs 208g.

**[0079]** Figure 4G shows an original substrate 210 and the blue micro-LEDs 211 thereof. The blue micro-LEDs to be lifted-off are aligned with the pads on the receiving substrate 204.

**[0080]** Figure 4H shows the situation in which the blue micro-LEDs 211 are in contact with the anisotropic conductive film 203 with a light force. At least one blue micro-LED is selectively lifted-off by using laser 212.

**[0081]** Figure 4F shows lifted-off red micro-LEDs 202r, green micro-LEDs 208g and blue micro-LEDs 211b.

**[0082]** After the transfer of micro-LEDs in the three colors, an inspection and repair can be performed with respect to any defect.

**[0083]** Figure 4J shows an auxiliary substrate 213. The auxiliary substrate 213 is a flat rigid substrate, such a glass substrate. Polymer 214 such as 3M LC5200/5320 is coated on the auxiliary substrate 213. The polymer can be cured through UV and can be de-bonded through red laser.

**[0084]** In Figure 4K, the ACF 203 is processed through the auxiliary substrate 213. For example, the processing condition is that the temperature is between 150°C and 200°C, the applied pressure is between 1 MPa and 4 MPa, the time period of applying pressure is between 10 second and 30 second. Through these processes, the ACF 203 interconnects the micro-LEDs with corresponding pad in the vertical direction.

**[0085]** Then, the auxiliary substrate 213 is de-bonded (through the polymer 214).

**[0086]** In Figure 4L, the normal subsequent processes are performed: etching the polymer 214, to expose the epitaxial layers of the micro-LEDs; forming N-metal electrodes 215 (for example, ITO electrodes) on the epitaxial layers of the micro-LEDs; and performing encapsulation 216 on the N-metal electrodes (for example, PET lamination).

**[0087]** Figure 5 shows a flow chart of still another example of a method for transferring a micro-LED not forming part of the present invention.

**[0088]** As shown in Figure 5, at step S3100, at least one micro-LED is transferred from an original substrate to a support body. For example, the original substrate is laser-transparent.

**[0089]** In an example, this step can comprises: mounting the original substrate onto the support body, wherein the micro-LEDs are formed on the original substrate, the support body has light-release adhesive on its surface, and the micro-LEDs are adhered to the support body via the light-release adhesive; irradiating the original substrate with laser from the original substrate side, for lifting-off the at least one micro-LED from the original substrate, and irradiating light from the support body side, to release un-lifted-off micro-LEDs. In this example, the support body is transparent.

**[0090]** For example, the light-release adhesive can be a UV tape. For example, the support body is stiff. The

displacement of micro-LEDs during transfer will have affect on the quality of the final product. The inventors of this application have found that this displacement can be reduced by using a stiff support body. For example, the material of the support body can be PET.

**[0091]** Generally, it is difficult to form red micro-LEDs on a laser-transparent substrate such as a sapphire substrate. Accordingly, in an example, the red micro-LEDs are formed in advance and then are transferred to an original substrate, for being finally transferred to a receiving substrate. For example, in this example, red micro-LEDs can be formed on a growth substrate. Then, the red micro-LEDs are transferred to an intermediate substrate. After that, the red micro-LEDs are transferred from the intermediate substrate to the original substrate.

**[0092]** At step S3200, the at least one micro-LED are transferred from the support body to a backup substrate.

**[0093]** For example, the backup substrate has elastomer or polymer on its surface. For example, the at least one micro-LED are bonded to the backup substrate through the elastomer or polymer.

**[0094]** In an example, this step can further comprises: bonding the support body with the at least one micro-LED to the backup substrate, and irradiating light from the support body side, to release the at least one micro-LED.

**[0095]** At step S3300, the at least one micro-LED are transferred from the backup substrate to a receiving substrate.

**[0096]** In an example, the step can further comprise: aligning the at least one micro-LED with the pads on the receiving substrate; and lifting-off the at least one micro-LED via the elastomer or polymer.

**[0097]** For example, the above transfer steps can be performed with respect to red micro-LEDs, blue micro-LEDs and green micro-LEDs, respectively. They will not be repeatedly described here.

**[0098]** After the above processes, normal subsequent processes can be done on the micro-LEDs. For example, the subsequent processes include: coating polymer on the receiving substrate with micro-LEDs; curing the polymer; etching the polymer, to expose the epitaxial layers of the micro-LEDs; forming N-metal electrodes on the epitaxial layers of the micro-LEDs; and performing encapsulation on the N-metal electrodes.

**[0099]** The inventors of this invention have found that during the transfer of micro-LEDs, usually, only part of the micro-LEDs on the original substrate are transferred. If the micro-LEDs are directly transferred to a receiving substrate, the remaining micro-LEDs on the original substrate are often contaminated. In this example, this contamination can be reduced through the transfer via an intermediate support body.

**[0100]** Generally, red micro-LEDs cannot be directly formed on a laser-transparent original substrate such as sapphire substrate. Thus, it is required that red micro-LEDs are formed on an additional substrate in advance, and then are transferred to a sapphire substrate. Figure

6A to 6F shows an example for transferring red micro-LEDs not forming part of the present invention.

**[0101]** As shown in Figure 6A, red micro-LEDs 302 are formed on a growth substrate 301 such as GaAs substrate.

**[0102]** As shown in Figure 6B, the red micro-LEDs 302 are bonded with intermediate substrate 304 such as silicon substrate, through temporary bonding polymer 303. The polymer 303 is a thermal release tape (TRT), for example.

**[0103]** As shown in Figure 6C, the growth substrate 301 is removed by a wet etching method, for example.

**[0104]** As shown in Figure 6D, a light resist 305 is coated on an original substrate 306 such as sapphire substrate. The original substrate 306 and the red micro-LEDs 302 are bonded through the resist 305. The resist 305 can endure the temperature above 200°C; generally above 250°C.

**[0105]** As shown in Figure 6E, the polymer 303 is processed under a temperature less than 200°C, to remove the intermediate substrate 304.

**[0106]** As shown in Figure 6F, a O<sub>2</sub> plasma etching is performed on the resist 305, to isolate the respective red micro-LEDs 302.

**[0107]** Figure 7A to 7L shows still another example for transferring a micro-LED not forming part of the present invention.

**[0108]** As shown in Figure 7A, the original substrate 406 has resist 405 and red micro-LEDs 402 thereon. The red micro-LEDs 402 are mounted onto a UV tape 411. The UV tape 411 is located on a stiff PET support body 402. The red micro-LEDs are selectively lifted-off through laser 413.

**[0109]** As shown in Figure 7B, a ultraviolet is irradiated from the support body 412 side, to release un-lifted-off red micro-LEDs.

**[0110]** The lifted-off red micro-LEDs 402r are easily separated from the original substrate 406. As shown in Figure 7C, the lifted-off red micro-LEDs 402r are adhered on the UV tape 411, while other red micro-LEDs remain on the original substrate 406.

**[0111]** As shown in Figure 7D, the backup substrate 415 such as glass substrate has elastomer/polymer 416 thereon. For example, the elastomer/polymer 416 is coated on the backup substrate 415 through spin coating. For example, the elastomer/polymer 416 is PDMS or 3M LC 5320, and can be cured through ultraviolet, for example.

**[0112]** As shown in Figure 7E, the support body is fully irradiated with ultraviolet, to release the red micro-LEDs and elastomer/polymer 416.

**[0113]** After that, for example, if the micro-LEDs do not have bumps thereon, the micro-LEDs on the backup substrate 415 can be screen-printed using silver paste.

**[0114]** As shown in 7F, the red micro-LEDs on the backup substrate 415 are aligned with the pads 419 on the receiving substrate 417. For example, the receiving substrate is a display substrate, and includes signal leads

418. For example, the red micro-LEDs are bonded to the pads 419 through reflow. The temperature of reflow can be more than 260°C. Then, the backup substrate 415 is separated from the receiving substrate 417 through laser lift-off.

**[0115]** Figure 7G shows separated receiving substrate 417. The receiving substrate 417 has pads 419 and red micro-LEDs 402r thereon.

**[0116]** Figure 7H shows a schematic diagram of transferring red micro-LEDs 422g from a backup substrate 420 to the receiving substrate 417. The backup substrate 420 has elastomer/polymer 421.

**[0117]** Figure 7I shows the separated receiving substrate 417. The receiving substrate 417 has pads 419, red micro-LEDs 402r and green micro-LEDs 402r thereon.

**[0118]** Figure 7J shows a schematic diagram of transferring blue micro-LEDs 425b from a backup substrate 423 to the receiving substrate 417. The backup substrate 423 has elastomer/polymer 424.

**[0119]** Figure 7K shows the separated receiving substrate 417. The receiving substrate 417 has pads 419, red micro-LEDs 402r, green micro-LEDs 402r and blue micro-LEDs 425b thereon

**[0120]** In Figure 7L, the normal subsequent processes are performed on the transferred micro-LEDs: coating polymer 426 on the receiving substrate with micro-LEDs; curing the polymer 426; etching the polymer, to expose the epitaxial layers of the micro-LEDs; forming N-metal electrodes 427 on the epitaxial layers of the micro-LEDs; and performing encapsulation (not shown) on the N-metal electrodes.

**[0121]** The present invention can use both vertical micro-LEDs and lateral micro-LEDs (flip-chip micro-LEDs). The micro-LEDs of vertical structure shown in the previous figures are illustrative and do not limit the scope of the present invention. Figure 8 shows an example of lateral micro-LEDs.

**[0122]** In the example of Figure 8, the micro-LEDs are lateral micro-LEDs. In the lateral micro-LEDs, the P electrodes and the N electrodes thereof are located on the same side. Figure 8 shows a red lateral micro-LED 505, a green lateral micro-LED 506 and a blue lateral micro-LED 507. The red lateral micro-LED 505 contains a P electrode 505p (positive electrode) and an N electrode 505n (negative electrode). The green lateral micro-LED 506 contains a P electrode 506p and an N electrode 506n. The blue lateral micro-LED 507 contains a P electrode 507p and an N electrode 507n.

**[0123]** Lead structures (including pads) 515p, 515n, 516p, 516n, 517p, 517n are provided in the substrate 504. The lead structures 515p, 516p, 517p are for connection with positive electrodes. The lead structures 515n, 516n, 517n are for connection with negative electrodes.

**[0124]** In the example of Figure 8, the electrodes 505p, 505n, 506p, 506n, 507p, 507n are connected to the lead structures 515p, 515n, 516p, 516n, 517p, 517n via an

anisotropic conductive layer 503.

**[0125]** Polymer 502 can be coated between the lateral micro-LEDs. A transparent cover 501 can be provided over the lateral micro-LEDs.

5 **[0126]** Figure 9 shows another example of lateral micro-LEDs. The difference between the example of Figure 9 and that of Figure 8 lies in that in Figure 9, the lateral micro-LEDs are connected to the substrate via solder rather than an anisotropic conductive layer.

10 **[0127]** Figure 9 shows a red lateral micro-LED 605, a green lateral micro-LED 606 and a blue lateral micro-LED 607. The red lateral micro-LED 605 contains a P electrode 605p and an N electrode 605n. The green lateral micro-LED 606 contains a P electrode 606p and an N electrode 606n. The blue lateral micro-LED 607 contains a P electrode 607p and an N electrode 607n.

15 **[0128]** Lead structures (including pads) 615p, 615n, 616p, 616n, 617p, 617n are provided in the substrate 604. The lead structures 615p, 616p, 617p are for connection with positive electrodes. The lead structures 615n, 616n, 617n are for connection with negative electrodes.

20 **[0129]** In the example of Figure 9, the electrodes 605p, 605n, 606p, 606n, 607p, 607n include solder bumps 602, for example. The solder bumps 602 are coated with flux, for example. The electrodes 605p, 605n, 606p, 606n, 607p, 607n are bonded to the lead structures 615p, 615n, 616p, 616n, 617p, 617n, for example, through reflow-soldering, respectively.

25 **[0130]** For example, polymer 603 can be filled between the lateral micro-LEDs and the substrate 604. A transparent cover 601 can be provided over the lateral micro-LEDs. These processes are well-known in the art and thus are not described in detail here.

30 **[0131]** Therefore, for example, the present invention can further include the specific application of lateral micro-LEDs.

35 **[0132]** A technical effect of using lateral micro-LEDs lies in that the processing for N metal electrode after the micro-LED transfer can be omitted. Furthermore, the wafer-level color-binning/testing can be simplified because the P electrodes and N electrodes already exist when a test at wafer-level is performed.

40 **[0133]** Furthermore, for example, in this method, an anisotropic conductive layer can be provided on a receiving substrate so as to bring the P electrodes and N electrodes of the lateral micro-LEDs into contact with the pads through the anisotropic conductive layer. Then, after lifting-off the lateral micro-LEDs from the original substrate, the anisotropic conductive layer is processed to electrically connect the P electrodes and N electrodes of the lateral micro-LEDs with the pads on the receiving substrate.

45 **[0134]** For example, the anisotropic conductive layer can be at least one of an anisotropic conductive film, an anisotropic conductive paste and an anisotropic conductive tape.

**[0135]** In addition to bringing the P electrodes and N

electrodes of the lateral micro-LEDs into contact with pads preset on a receiving substrate by the stickiness of an anisotropic conductive layer or by the surface tension of liquid (such as flux), the present invention can further realize the contact by actions of gravity, electrostatic force and/or electromagnetic force.

**[0136]** For example, when the original substrate is irradiated with laser from the original substrate side, the lateral micro-LEDs are separated from the original substrate and the lateral micro-LEDs are dropped off onto the receiving substrate because of gravity.

**[0137]** For example, electrostatic force can be applied by applying voltage to the pads, so that the lateral micro-LEDs are dropped off onto the receiving substrate after being lifted-off from the original substrate because of the electrostatic force.

**[0138]** For example, in case that the lateral micro-LEDs contains magnetic substance such as Ni, a magnetic field can be provided, so that the lateral micro-LEDs are dropped off onto the receiving substrate after being lifted-off from the original substrate because of the electromagnetic force.

**[0139]** Similarly, the transfer method in the example of using lateral micro-LEDs can be applied to a method for manufacturing a micro-LED device for transferring the lateral micro-LEDs onto a receiving substrate. For example, the receiving substrate is a display screen or display substrate. The micro-LED device is a display device, for example.

**[0140]** For example, a micro-LED device, such as a display device, can be manufactured by using the manufacturing method. The micro-LED device adopts lateral micro-LEDs.

**[0141]** Figure 10 shows a flow chart of a method for transferring micro-LEDs by means of a contactless force which may be used as a part of the method for transferring micro-LEDs at wafer level according to the present invention.

**[0142]** As shown in Figure 10, in the method for transferring micro-LEDs, at step S4100, micro-LEDs are formed on a laser-transparent original substrate.

**[0143]** The micro-LEDs can be lateral micro-LEDs or can be micro-LEDs of vertical structure. In a lateral micro-LED, the P electrodes and N electrodes thereof are located on one same side. In a micro-LED of vertical structure, the P electrodes and N electrodes thereof are located on opposite sides.

**[0144]** At step S4200, the original substrate is irradiated with laser from the original substrate side to lift-off the micro-LEDs from the original substrate.

**[0145]** At step S4300, the micro-LEDs are brought into contact with pads preset on a receiving substrate through a contactless force.

**[0146]** The contactless force means that the action per se can be applied without the direct contact of objects. For example, the contactless force can be applied by means of a field. This is different from the action applied through the stickiness of an anisotropic conductive layer

or by the surface tension of liquid (such as flux). It should be understood that although the contactless force per se can be applied without the direct contact of objects, the direct contact of objects can be kept through the contactless force. For example, several example of the contactless force are given as below.

**[0147]** For example, the contactless force is gravity. The micro-LEDs are placed over the receiving substrate. When the lift-off is performed, the micro-LEDs are dropped off on the receiving substrate and is left on the receiving substrate.

**[0148]** For example, the contactless force is electrostatic force. The electrostatic force can be applied by applying voltage to the pads.

**[0149]** For example, the contactless force is electromagnetic force. In case that the micro-LEDs contains magnetic substance, a magnetic field can be provided by means of a magnet such as permanent magnet, so that the micro-LEDs are dropped off and are left onto the receiving substrate after being lifted-off from the original substrate because of the electromagnetic force, thereby contacting with the pads directly or indirectly.

**[0150]** In this example, the micro-LEDs are attached onto the receiving substrate via a contactless manner.

**[0151]** For example, the electrodes of the micro-LEDs include solder bumps. The solder bumps are bonded with the pads, for example, through reflow-soldering and so on.

**[0152]** The order of steps in Figure 10 will not constitute any limitation of the present invention. For example, although the step S4200 are shown in front of the step S4030, the action of gravity, the action of electrostatic force or the action of electromagnetic force can be applied before the step S4200 or at the time when performing the step S4200. In another word, for example, the step S4300 can be performed before the step S4200 or simultaneously with the step S4200.

**[0153]** Similarly, the transfer method can be applied to a method for manufacturing a micro-LED device for transferring the micro-LEDs onto a receiving substrate. For example, the receiving substrate is a display screen or display substrate. The micro-LED device is a display device, for example.

**[0154]** For example, a micro-LED device, such as a display device, can be manufactured by using the manufacturing method.

**[0155]** Figure 11 shows a flow chart of still another illustrative example of a method not forming part of the present invention.

**[0156]** As shown in Figure 11, at step S5100, a micro-LED defect pattern on a receiving substrate is obtained.

**[0157]** For example, the defect pattern can be obtained through an automatic visual inspection (AVI), a photoluminescence (PL), an electro-optical test, or an electric-performance test, etc. These detection approaches are not described here in details.

**[0158]** At step S5200, micro-LEDs corresponding to the defect pattern are formed on a laser-transparent re-



pair carrier substrate.

**[0159]** In an example, the micro-LEDs can first be mounted onto a temporary substrate in the defect pattern.

**[0160]** For example, the temporary substrate is rigid, such as a PET plate. For example, an adhesive, such as an UV tape, is coated on the temporary substrate. The micro-LEDs on a laser-transparent original substrate can be brought into contact with the adhesive. Then, the original substrate is irradiated with laser in the defect pattern, to lift-off the micro-LEDs from the original substrate. The lifted-off micro-LEDs in the defect pattern are kept on the temporary substrate while the un-lifted-off micro-LEDs are released through a partial adhesive releasing. After the partial adhesive releasing, the un-lifted-off micro-LEDs remain on the original substrate. The partial adhesive releasing means that after the releasing, the residual stiction of the adhesive is sufficient to separate the lifted-off micro-LEDs from the original substrate while it cannot separate the un-lifted-off micro-LEDs from the original substrate.

**[0161]** Next, the micro-LEDs on the temporary substrate are transferred to the repair carrier substrate.

**[0162]** For example, the micro-LEDs on the temporary substrate can first be bonded onto the repair carrier substrate. The micro-LEDs on the temporary substrate can be bonded onto the repair carrier substrate through a polymer thin film, for example. Then, the micro-LEDs is lifted-off from the temporary substrate through a complete adhesive releasing. For example, after the micro-LEDs is lifted-off from the temporary substrate, at least one part of the polymer thin film is removed, such as the polymer thin film portion between micro-LEDs.

**[0163]** For example, the partial adhesive releasing and the complete adhesive releasing can be performed through UV exposure.

**[0164]** Generally, the exposure time or energy used in the partial adhesive releasing is less than the standard exposure time or energy, i.e. the exposure time in the partial releasing is less than the standard time and/or the energy in the partial releasing is less than the standard energy. The exposure time or energy used in the complete adhesive releasing is higher than or equal to the standard exposure time or energy, i.e. the exposure time in the complete releasing is larger than or equal to the standard time and/or the energy in the complete releasing is larger than or equal to the standard energy. The standard exposure time or energy can be the exposure time or energy just releasing the adhesive completely, or can be the nominal exposure time or energy.

**[0165]** At step S5300, the micro-LEDs on the repair carrier substrate are aligned with the defect positions on the receiving substrate, and the micro-LEDs are brought into contact with the pads at the defect positions.

**[0166]** At step S5400, the repair carrier substrate is irradiated with laser from the repair carrier substrate side, to lift-off the micro-LEDs from the repair carrier substrate.

**[0167]** For example, the repair carrier substrate is a sapphire substrate. In the present invention, the original

substrate adopted is laser-transparent. That is, compared with the device such as a micro-LED to be lifted off, the original substrate is transparent with respect to the laser to be irradiated, i.e. the original substrate has a higher transmittance. Accordingly, the energy in the laser will be mainly absorbed by the device (such as a micro-LED) behind it when it is irradiated, to achieve the lift-off. Of course, the larger the transmittance difference between the laser-transparent original substrate and the device is, the better the lift-off effect is.

**[0168]** After micro-LEDs of large scale are transferred to a receiving substrate, a yield loss to a certain degree will arise. Thus, a repair is necessary at most cases to guarantee the product quality. In the prior art, a pick-up head is used to perform the repair. The repair approach of the prior is relatively complicated and the efficiency thereof is relatively low. The repair approach of this invention is relatively simple and/or has a relatively high efficiency.

**[0169]** Figures 12A to 12F show an example for repairing micro-LED defects not forming part of the present invention.

**[0170]** As shown in Figure 12A, micro-LEDs 703 are formed on an original substrate 701. The micro-LEDs 703 include defect micro-LEDs and good micro-LEDs. The micro-LEDs are mounted onto a temporary substrate 705 through an adhesive layer 704. The adhesive layer 704 is an UV tape for example. The temporary substrate 705 is a PET plate, for example. The original substrate 701 is irradiated with laser 702 in a defect pattern, to lift off the defect micro-LEDs from the original substrate.

**[0171]** As shown in Figure 12B, the adhesive layer (the UV tape) 704 is partially exposed with an ultra violet radiation 706 from the side of the temporary substrate 705.

**[0172]** As shown in Figure 12C, after the partial exposure, the adhesive layer 704 still remain a certain residual stiction sufficient to separate the laser-lifted-off micro-LEDs 703b from the original substrate, while leaving the un-laser-lifted-off micro LEDs 703a on the original substrate. Since the micro-LEDs are lifted off with laser in the defect pattern, the adhesive layer 704 (or the temporary substrate 705) has good micro-LEDs arranged in the defect pattern thereon.

**[0173]** As shown in Figure 12D, the micro-LEDs 703b on the adhesive layer 704 are temporarily bonded onto a repair carrier substrate 707 through a polymer thin film 708. Then, the adhesive layer 704 is completely exposed. As shown in Figure 12E, the adhesive layer 704 is separated from the micro-LEDs 703b. Figure 12F shows the repair carrier substrate 707 and the micro-LEDs 703b in the defect pattern thereon for repairing. As shown in Figure 12F, the bonding polymer thin film 708 between the micro-LEDs 703b can be removed, leaving the thin film portions between the micro-LEDs 703b and the substrate 707.

**[0174]** Next, the repair carrier substrate 707 can be used for repairing the defects on a receiving substrate by means of laser lifting-off.

**[0175]** Figure 13 shows a flow chart of the method for pre-screening defect micro-LEDs of still another illustrative example not forming part of the present invention.

**[0176]** As shown in Figure 13, at step S6100, a defect pattern of defect micro-LEDs on a laser-transparent substrate is obtained.

**[0177]** For example, the defect pattern can be obtained through an automatic visual inspection, a photoluminescence, an electro-optical test, or an electric-performance test.

**[0178]** At step S6200, the laser-transparent substrate is irradiated with laser from the laser-transparent substrate side in accordance with the defect pattern, to lift-off the defect micro-LEDs from the laser-transparent substrate.

**[0179]** In an example, an action is applied through a contact manner to separate the lifted-off micro-LEDs from the laser-transparent substrate. For example, the micro-LEDs on the laser-transparent substrate can be mounted onto an UV tape. For example, the UV tape is attached onto a rigid support body. The defect micro-LEDs are lifted-off through laser to the UV tape and the non-defect micro-LEDs are kept on the laser-transparent substrate though an UV exposure.

**[0180]** In another example, the defect micro-LEDs can be lifted-off from the laser-transparent substrate through a contactless force. As described above, the contactless force is applied without contact. For example, the contactless force is at least one of gravity, electrostatic force and electromagnetic force. These actions can be applied according to the manner described above.

**[0181]** A repair can be performed after the micro-LEDs are transferred to the receiving substrate, or a repair can be performed on the laser-transparent substrate before the transfer. For example, good micro-LEDs are formed at the position of the lifted-off micro-LEDs on the laser-transparent substrate. The good micro-LEDs can be formed at the defect positions by using the repairing method described above.

**[0182]** Figures 14A to 14C show an example for pre-screening defect micro-LEDs not forming part of the present invention.

**[0183]** In this example, the defect pattern on a laser-transparent substrate is obtained through an automatic visual inspection (AVI), a photoluminescence (PL), an electro-optical test, or an electric-performance test, etc. Then, the laser-transparent substrate is mounted onto a UV tape. As shown in Figure 14A, the UV tape 804 is placed on a support body 805. The laser-transparent substrate 801 is mounted onto the UV tape 804 via micro-LEDs 803. The substrate 801 is irradiated with laser in the defect pattern, to lift off the defect micro-LEDs from the substrate 801.

**[0184]** As shown in Figure 14B, the UV tape 804 is partially exposed with an ultra violet radiation 806 from the side of the support body 805.

**[0185]** As shown in Figure 14C, after the partial exposure, the UV tape 804 still remains a certain residual stic-

tion sufficient to separate the laser-lifted-off micro-LEDs 803b from the substrate 801, while leaving the un-laser-lifted-off micro-LEDs 803a on the substrate 801.

**[0186]** Figures 15A to 15B show another example for pre-screening defect micro-LEDs not forming part of the present invention.

**[0187]** As shown in Figure 15A, the substrate (wafer) 901 has good micro-LEDs 902 and defect micro-LEDs 903 thereon. The defect micro-LEDs 903 are pre-screened before the micro-LEDs are transferred from the substrate 901 to a receiving substrate (not shown). Figure 15B shows the substrate 901 after the defect micro-LEDs are pre-screened.

**[0188]** Figures 16A to 16B is an enlarged view of the area "A" of Figure 15B. As shown in Figure 16A, the defect micro-LED at the position 903a is pre-screened. As shown in Figure 16B, a repair can be performed directly on the substrate 901, to form a good micro-LED at the position 903a. Alternatively, the repair can be performed after the micro-LEDs are transferred from the substrate 901 to a receiving substrate.

**[0189]** Figure 17 shows a flow chart of an embodiment of the method for transferring micro-LED at wafer level according to the present invention.

**[0190]** As shown in Figure 17, at step S7100, micro-LEDs on a laser-transparent original substrate are temporarily bonded onto a carrier substrate via a first bonding layer.

**[0191]** For example, the first bonding layer can be a UV or light releasable tape. For example, the carrier substrate can be a PET plate. The PET plate is rigid and can provide a sufficient support to the UV or light releasable tape to prevent a displacement of the transferred micro-LEDs.

**[0192]** At step S7200, the original substrate is irradiated from the original substrate side with laser, to lift-off selected micro-LEDs from the original substrate.

**[0193]** At step S7300, a partial release is performed on the first bonding layer, to transfer the selected micro-LEDs to the carrier substrate.

**[0194]** For example, the release degree of the first bonding layer can be controlled by controlling the intensity and/or the irradiation time of the UV or light irradiating the first bonding layer.

**[0195]** In an example, in order to sufficient guarantee the transfer of the lifted-off micro-LEDs onto the carrier substrate, a contactless force can be applied onto the micro-LEDs during the partial release. For example, the contactless force is at least one of gravity, electrostatic force and electromagnetic force.

**[0196]** At step S7400, the micro-LEDs on the carrier substrate are temporarily bonded onto a transfer head substrate via a second bonding layer.

**[0197]** At step S7500, a full release is performed on the first bonding layer, to transfer the micro-LEDs to the transfer head substrate.

**[0198]** For example, the partial release and the full release are performed by exposure using UV or light.

**[0199]** At step S7600, the micro-LEDs on the transfer head substrate is bonded onto a receiving substrate.

**[0200]** At step S7700, the transfer head substrate is removed by releasing the second bonding layer, to transfer the micro-LEDs to the receiving substrate.

**[0201]** For example, the second bonding layer can be released by a thermal release.

**[0202]** In a preferred embodiment, the transferred micro-LEDs are vertically structured. The vertically-structured micro-LEDs can provide a display panel with a higher resolution. The vertically-structured micro-LEDs are un-finished micro-LEDs. So, after the micro-LEDs are transferred to the receiving substrate, N electrodes are formed on the micro-LEDs on the receiving substrate and an encapsulation is performed on the N electrodes, to form complete micro-LEDs.

**[0203]** In order to improve the yield of the display panel, the micro-LEDs can be arranged on the receiving substrate in a redundant manner.

**[0204]** In another embodiment, the present invention further provides a method for manufacturing a micro-LED device. The manufacturing method comprises transferring micro-LEDs onto a receiving substrate of the micro-LED device by using the method for transferring micro-LED at wafer level according to this embodiment. For example, the receiving substrate is a display screen or display substrate. The micro-LED device is a display device, for example.

**[0205]** Figures 18A to 18J show an embodiment for transferring micro-LEDs at wafer level according to the present invention.

**[0206]** As shown in Figure 18A, micro-LEDs are formed on a laser-transparent original substrate 1001. Figure 18A shows red micro-LEDs 1003r. The original substrate 1001 is a sapphire substrate, for example.

**[0207]** The micro-LEDs 1003r are temporarily bonded onto a carrier substrate 1005 via a first bonding layer 1004. For example, the first bonding layer 1004 can be a UV or light releasable tape. For example, the carrier substrate can be a PET plate.

**[0208]** In Figure 18A, the original substrate 1001 is irradiated from the original substrate side with laser 1002, to lift-off selected micro-LEDs from the original substrate.

**[0209]** In Figure 18B, a partial release is performed on the first bonding layer 1004. As shown in Figure 18C, the selected micro-LEDs 1003r are transferred to the carrier substrate 1005.

**[0210]** For example, the release degree of the first bonding layer 1004 can be controlled by controlling the intensity and/or the irradiation time of the UV or light 1006 irradiating the first bonding layer.

**[0211]** In order to improve the effect of the release, a contactless force can be applied onto the micro-LEDs during the partial release. For example, the contactless force is at least one of gravity, electrostatic force and electromagnetic force.

**[0212]** Next, in Figure 18D, the micro-LEDs 1003r are temporarily bonded onto a transfer head substrate 1008

via a second bonding layer 1007.

**[0213]** In Figure 18E, a full release is performed on the first bonding layer 1004. In Figure 18F, the micro-LEDs 1003r are transferred to the transfer head substrate 1008.

**[0214]** For example, the partial release and the full release can be performed by exposure using UV or light.

**[0215]** Figures 18G and 18H show a transfer head substrate 1010 and a transfer head substrate 1012, respectively. The transfer head substrate 1010 has green micro-LEDs 1003g and a second bonding layer 1009. The transfer head substrate 1012 has blue micro-LEDs 1003b and a second bonding layer 1011.

**[0216]** In Figure 18I, the micro-LEDs 1003r on the transfer head substrate is bonded onto a receiving substrate 1013 for finishing the transfer.

**[0217]** In Figure 18J, the second bonding layer is released and the transfer head substrate is removed. The red, green and blue micro-LEDs 1003r, 1003g, 1003b are transferred to the receiving substrate 1013.

**[0218]** For example, the second bonding layer can be released by a thermal release.

**[0219]** The above micro-LEDs can be vertically structured. So, after the micro-LEDs are transferred to the receiving substrate 1013, N electrodes are formed on the micro-LEDs and an encapsulation is performed on the N electrodes, to form complete micro-LEDs (not shown).

**[0220]** Although some specific embodiments of the present invention have been described in detail, it should be understood by a person skilled in the art that the above embodiments are only intended to be illustrative but not to limit the scope of the present invention. It should be understood by a person skilled in the art that the above embodiments can be modified without departing from the scope of the present invention which is defined by the attached claims.

## Claims

1. A method for transferring micro-LEDs (1003r, 1003g, 1003b) at wafer level, comprising:

temporarily bonding micro-LEDs (1003r, 1003g, 1003b) on a laser-transparent original substrate (1001) onto a carrier substrate (1005) via a first bonding layer (1004) (S7100);

irradiating the original substrate (1001) from the original substrate side with laser (1002), to lift-off selected micro-LEDs (1003r, 1003g, 1003b) from the original substrate (1001) (S7200);

performing a partial release on the first bonding layer (1004), to transfer the selected micro-LEDs (1003r, 1003g, 1003b) to the carrier substrate (1005) (S7300);

temporarily bonding the selected micro-LEDs (1003r, 1003g, 1003b) on the carrier substrate (1005) onto a transfer head substrate (1008, 1010, 1012) via a second bonding layer (1007,

- 1009, 1011) (S7400);  
 performing a full release on the first bonding layer (1004), to transfer the selected micro-LEDs (1003r, 1003g, 1003b) to the transfer head substrate (1008, 1010, 1012) (S7500);  
 bonding the selected micro-LEDs (1003r, 1003g, 1003b) on the transfer head substrate (1008, 1010, 1012) onto a receiving substrate (1013) (S7600); and  
 removing the transfer head substrate (1008, 1010, 1012) by releasing the second bonding layer (1007, 1009, 1011), to transfer the selected micro-LEDs (1003r, 1003g, 1003b) to the receiving substrate (1013) (S7700).
2. The method according to claim 1, wherein the micro-LEDs (1003r, 1003g, 1003b) are vertically-structured micro-LEDs (1003r, 1003g, 1003b), and the method further comprises:
- forming N electrodes on the micro-LEDs (1003r, 1003g, 1003b) on the receiving substrate (1013); and  
 performing encapsulation on the N electrodes.
3. The method according to claim 1, wherein the first bonding layer (1004) is a UV or light releasable tape.
4. The method according to claim 3, wherein the carrier substrate (1005) is a PET plate.
5. The method according to claim 1, wherein the partial release and the full release are performed by light exposure.
6. The method according to claim 1, wherein the second bonding layer (1007, 1009, 1011) is released by thermal release.
7. The method according to claim 1, wherein the selected micro-LEDs (1003r, 1003g, 1003b) are arranged on the receiving substrate (1013) in a redundant manner.
8. The method according to claim 1, wherein a contactless force is applied onto the micro-LEDs (1003r, 1003g, 1003b) during the partial release.
9. The method according to claim 8, wherein the contactless force is at least one of gravity, electrostatic force and electromagnetic force.
10. A method for manufacturing a micro-LED device, comprising transferring micro-LEDs (1003r, 1003g, 1003b) onto a receiving substrate (1013) of the micro-LED device by using the method according to claim 1.

## Patentansprüche

1. Verfahren zum Übertragen von Mikroleuchtdioden (1003r, 1003g, 1003b) auf Waferebene, umfassend:
- vorübergehendes Verbinden von Mikroleuchtdioden (1003r, 1003g, 1003b) auf einem lasertransparenten Originalsubstrat (1001) mittels einer ersten Verbindungsschicht (1004) auf ein Trägersubstrat (1005) (S7100);  
 Bestrahlen des Originalsubstrats (1001) von der Seite des Originalsubstrats mit einem Laser (1002), um ausgewählte Mikroleuchtdioden (1003r, 1003g, 1003b) vom Originalsubstrat (1001) abzutrennen (S7200);  
 Durchführen einer teilweisen Freigabe der ersten Verbindungsschicht (1004), um die ausgewählten Mikroleuchtdioden (1003r, 1003g, 1003b) auf das Trägersubstrat (1005) zu übertragen (S7300);  
 vorübergehendes Verbinden der ausgewählten Mikroleuchtdioden (1003r, 1003g, 1003b) auf dem Trägersubstrat (1005) mittels einer zweiten Verbindungsschicht (1007, 1009, 1011) auf ein Übertragungskopfsubstrat (1008, 1010, 1012) (S7400);  
 Durchführen einer vollständigen Freigabe der ersten Verbindungsschicht (1004), um die ausgewählten Mikroleuchtdioden (1003r, 1003g, 1003b) auf das Übertragungskopfsubstrat (1008, 1010, 1012) zu übertragen (S7500);  
 Verbinden der ausgewählten Mikroleuchtdioden (1003r, 1003g, 1003b) auf dem Übertragungskopfsubstrat (1008, 1010, 1012) auf ein Empfangssubstrat (1013) (S7600); und  
 Entfernen des Übertragungskopfsubstrats (1008, 1010, 1012) durch Freigeben der zweiten Verbindungsschicht (1007, 1009, 1011), um die ausgewählten Mikroleuchtdioden (1003r, 1003g, 1003b) auf das Empfangssubstrat (1013) zu übertragen (S7700).
2. Verfahren nach Anspruch 1, wobei die Mikroleuchtdioden (1003r, 1003g, 1003b) vertikal strukturierte Mikroleuchtdioden (1003r, 1003g, 1003b) sind, und das Verfahren ferner umfasst:  
 Bilden von N Elektroden auf den Mikroleuchtdioden (1003r, 1003g, 1003b) auf dem Empfangssubstrat (1013); und Durchführen einer Einkapselung auf den N Elektroden.
3. Verfahren nach Anspruch 1, wobei die erste Verbindungsschicht (1004) ein durch UV oder Licht freigegebenes Band ist.
4. Verfahren nach Anspruch 3, wobei das Trägersubstrat (1005) eine PET-Platte ist.

5. Verfahren nach Anspruch 3, wobei die teilweise Freigabe und die vollständige Freigabe durch Belichtung durchgeführt werden.
6. Verfahren nach Anspruch 1, wobei die zweite Verbindungsschicht (1007, 1009, 1011) mittels einer thermischen Freigabe freigegeben wird. 5
7. Verfahren nach Anspruch 1, wobei die ausgewählten Mikroleuchtdioden (1003r, 1003g, 1003b) in einer redundanten Weise auf dem Empfangssubstrat (1013) angeordnet sind. 10
8. Verfahren nach Anspruch 1, wobei während der Durchführung der teilweisen Freigabe eine berührungslose Kraft auf die Mikroleuchtdioden (1003r, 1003g, 1003b) ausgeübt wird. 15
9. Verfahren nach Anspruch 8, wobei die berührungslose Kraft zumindest eine von einer Schwerkraft, einer elektrostatischen Kraft und einer elektromagnetischen Kraft ist. 20
10. Verfahren zur Herstellung einer Mikroleuchtdiodenvorrichtung, umfassend das Übertragen von Mikroleuchtdioden (1003r, 1003g, 1003b) auf das Empfangssubstrat (1013) der Mikroleuchtdiodenvorrichtung unter Verwendung des Verfahrens nach Anspruch 1. 25

## Revendications

1. Procédé de transfert des micro-diodes électroluminescentes (1003r, 1003g, 1003b) au niveau de la plaquette, comprenant : 35
 

des micro-diodes électroluminescentes (1003r, 1003g, 1003b) sur un substrat original (1001) transparent au laser sont temporairement liées au substrat porteur (1005) via une première couche de liaison (1004) (S7100) ;

Le substrat original (1001) est irradié avec un laser du côté du substrat original, pour décoller les micro-diodes électroluminescentes (1003r, 1003g, 1003b) sélectionnées du substrat original (1001) (S7200) ;

Une libération partielle est exécutée sur la première couche de liaison (1004), pour transférer ainsi les micro-diodes électroluminescentes (1003r, 1003g, 1003b) sélectionnées sur le substrat porteur (1005) (S7300) ;

Les micro-diodes électroluminescentes (1003r, 1003g, 1003b) sélectionnées sur le substrat porteur (1005) sont temporairement liées à un substrat de tête de transfert (1008, 1010, 1012) via une deuxième couche de liaison (1007, 1009, 1011) (S7400) ;

Une libération totale est exécutée sur la première couche de liaison (1004), pour transférer les micro-diodes électroluminescentes (1003r, 1003g, 1003b) sélectionnées sur le substrat de tête de transfert (1008, 1010, 1012) (S7500) ;

Les micro-diodes électroluminescentes (1003r, 1003g, 1003b) sélectionnées sur le substrat de tête de transfert (1008, 1010, 1012) sont liées à un substrat de réception (1013) (S7600) ; et

Le substrat de tête de transfert (1008, 1010, 1012) est retiré en libérant la deuxième couche de liaison (1007, 1009, 1011), pour transférer ainsi les micro-diodes électroluminescentes (1003r, 1003g, 1003b) sélectionnées au substrat de réception (1013) (S7700).

2. Procédé selon la revendication 1, dans lequel lesdites micro-diodes électroluminescentes (1003r, 1003g, 1003b) sont des micro-diodes électroluminescentes (1003r, 1003g, 1003b) à structure verticale, et ledit procédé comprend en outre :

formant des électrodes N sur les micro-diodes électroluminescentes (1003r, 1003g, 1003b) sur le substrat de réception (1013) ; et encapsulant sur les électrodes N.

3. Procédé selon la revendication 1, dans lequel ladite première couche de liaison (1004) est une bande adhésif à libération d'UV ou une bande adhésif à libération optique. 30
4. Procédé selon la revendication 3, dans lequel ledit substrat porteur (1005) est une plaque en PET.
5. Procédé selon la revendication 3, dans lequel ladite libération partielle et ladite libération totale sont effectuées par exposition.
6. Procédé selon la revendication 1, dans lequel ladite deuxième couche de liaison (1007, 1009, 1011) est libérée par dégagement de chaleur.
7. Procédé selon la revendication 1, dans lequel les micro-diodes électroluminescentes (1003r, 1003g, 1003b) sélectionnées sont agencées sur le substrat de réception (1013) de manière redondante. 45
8. Procédé selon la revendication 1, dans lequel une force sans contact est appliquée auxdites micro-diodes électroluminescentes (1003r, 1003g, 1003b) lors de l'exécution de la libération partielle. 50
9. Procédé selon la revendication 8, dans lequel ladite force sans contact est au moins l'un des suivants : une gravité, une force électrostatique et une force électromagnétique. 55

10. Procédé de fabrication d'un dispositif à micro-diodes électroluminescentes, comprenant le transfert des micro-diodes électroluminescentes (1003r, 1003g, 1003b) sur un substrat de réception (1013) du dispositif à micro-diodes électroluminescentes en utilisant le procédé selon la revendication 1.

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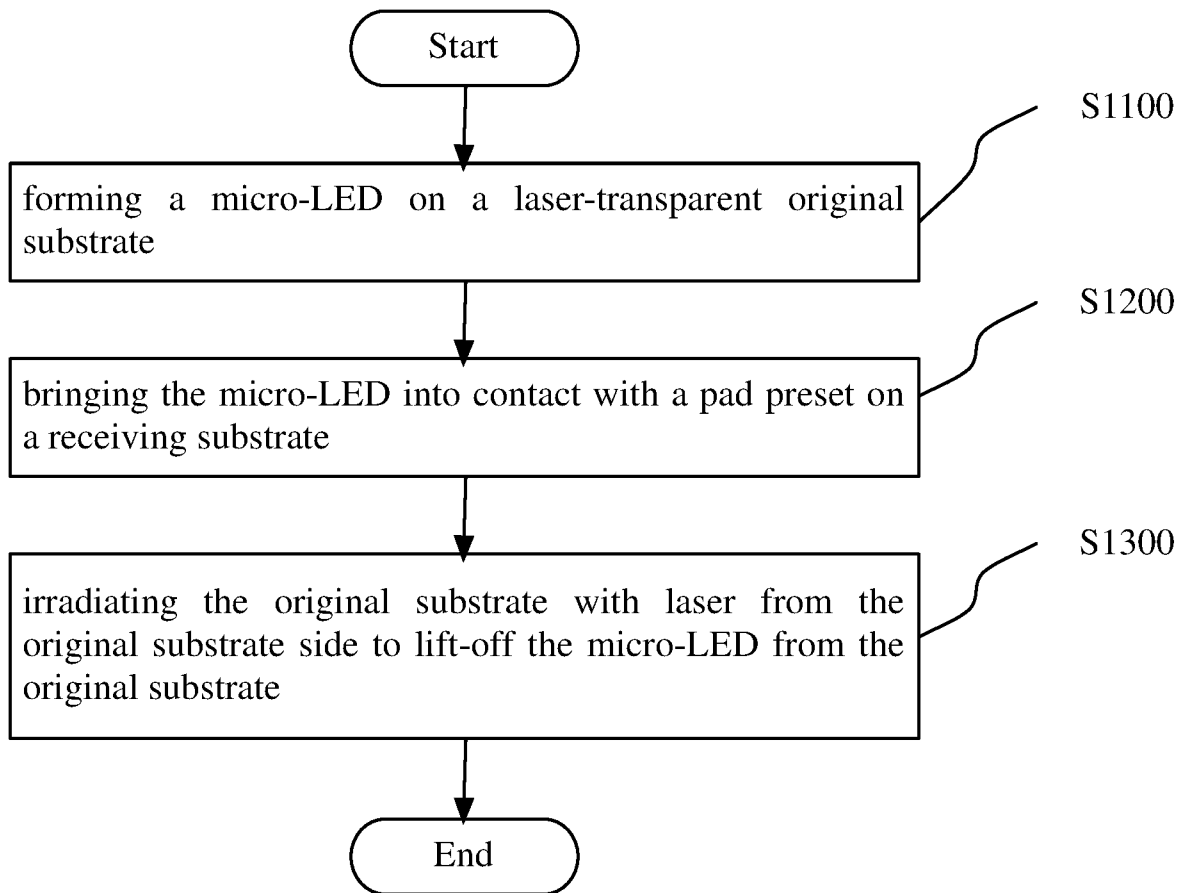


FIG. 1

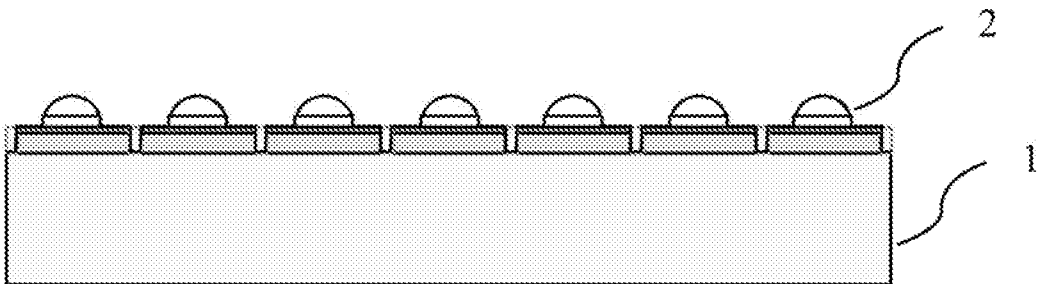


FIG. 2A

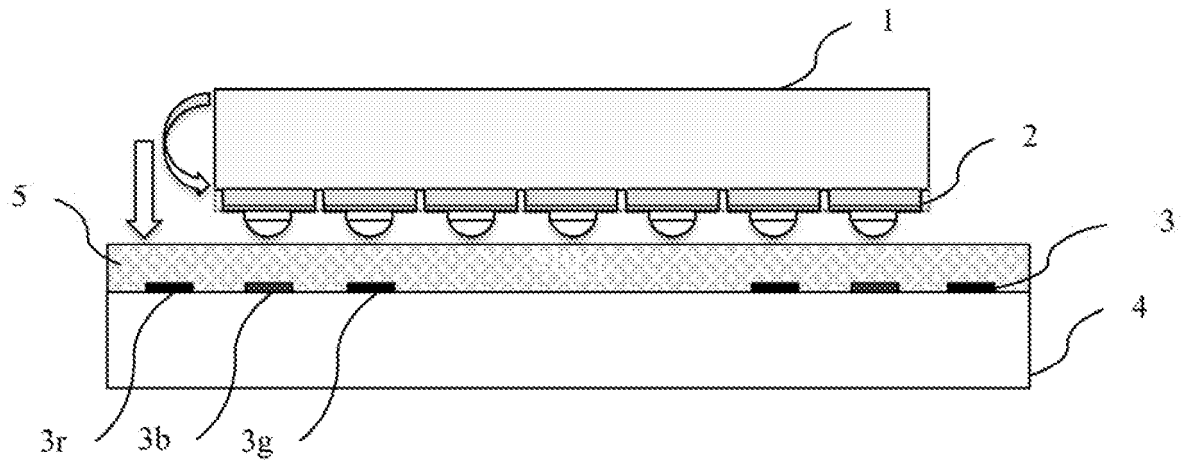


FIG. 2B

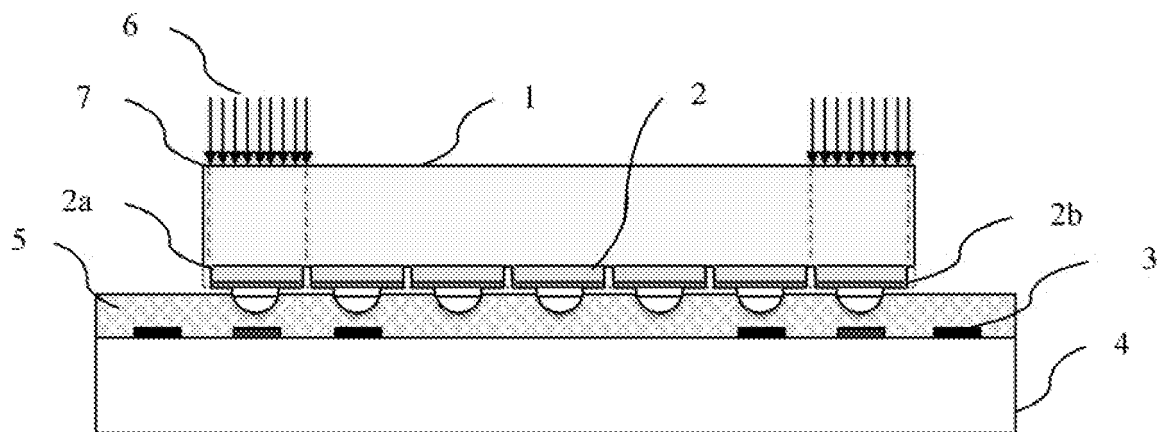


FIG. 2C



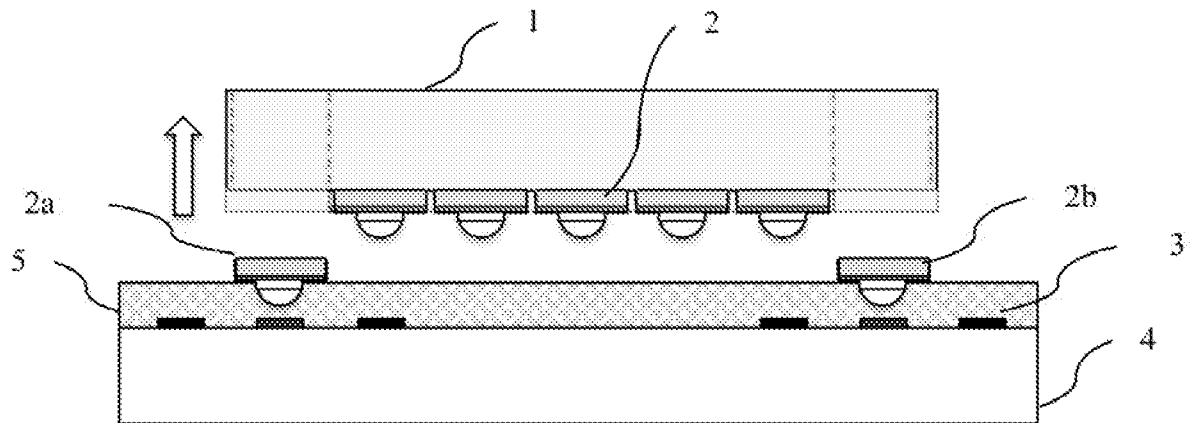


FIG. 2D

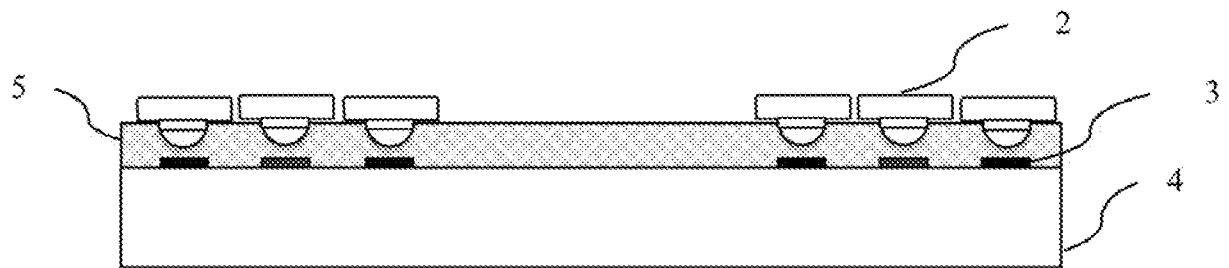


FIG. 2E

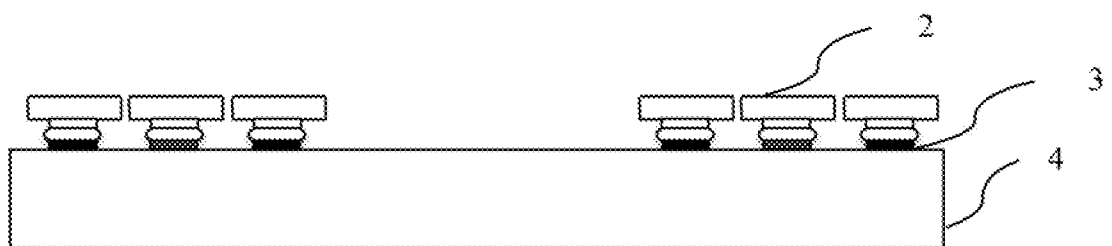
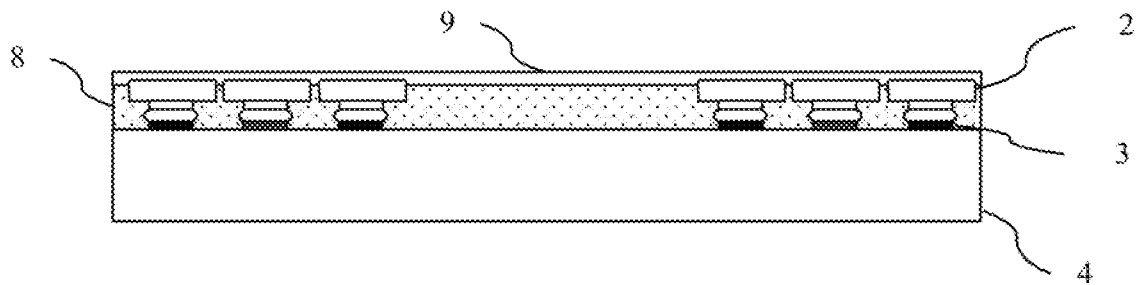
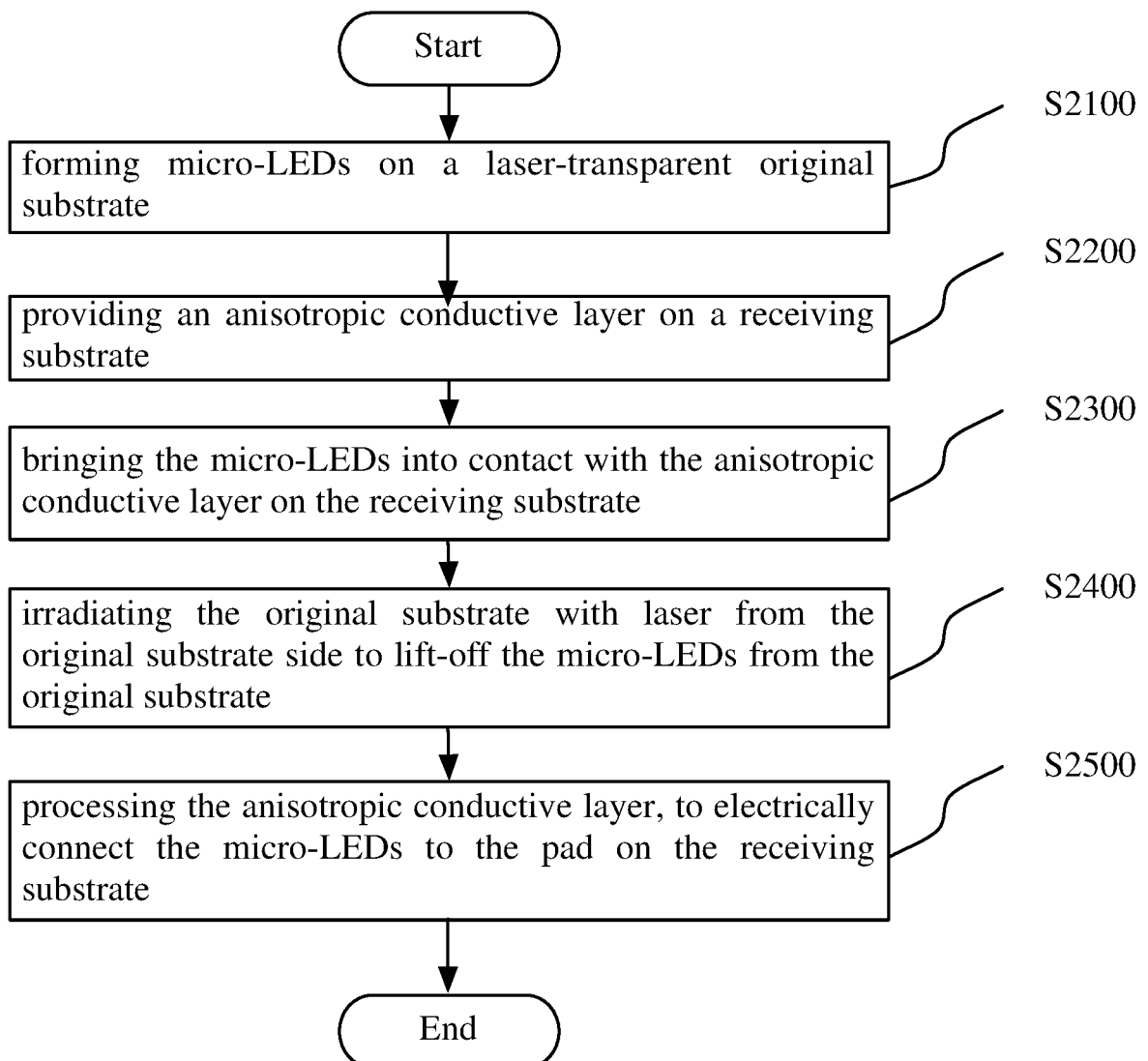


FIG. 2F



**FIG. 2G**



**FIG. 3**

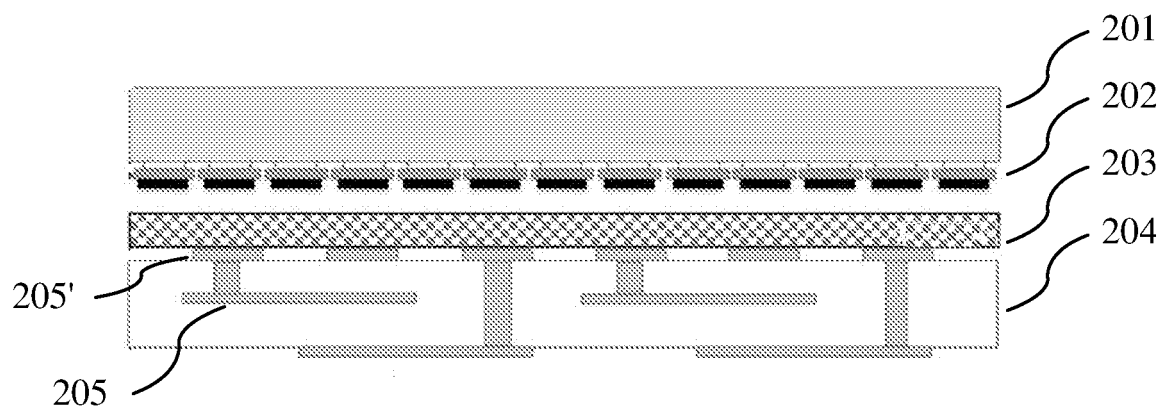


FIG. 4A

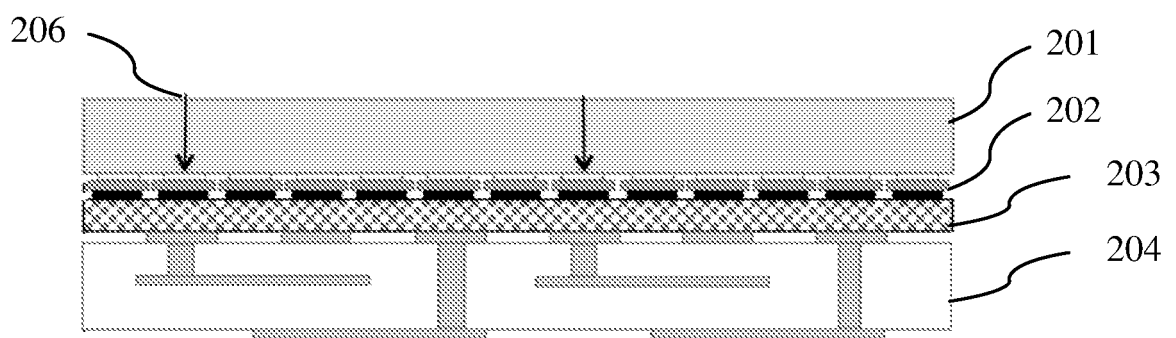


FIG. 4B

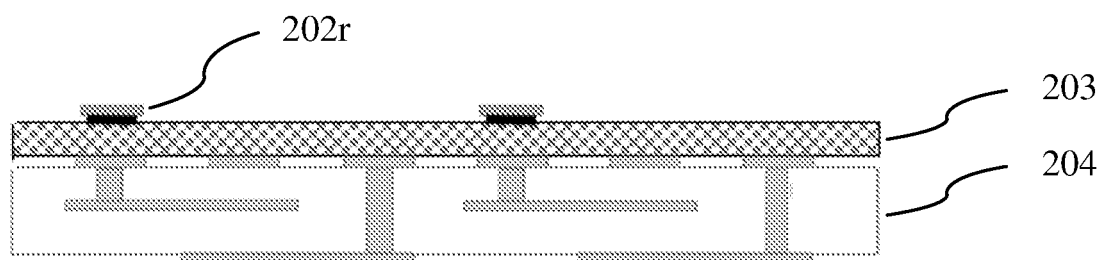


FIG. 4C

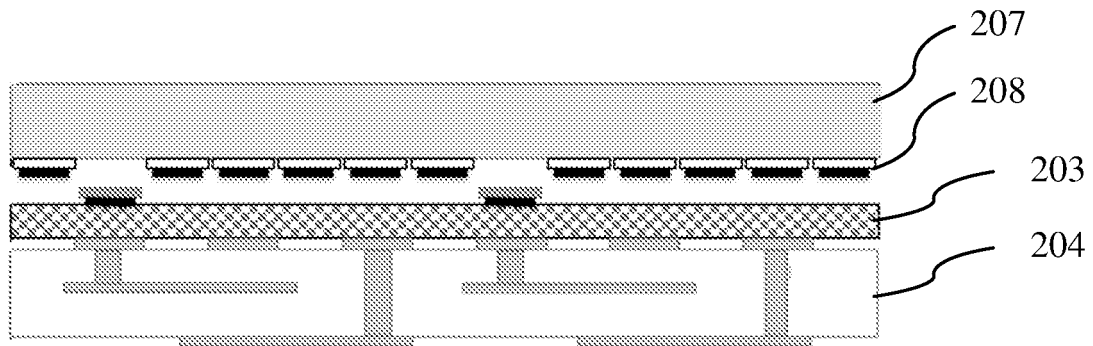


FIG. 4D

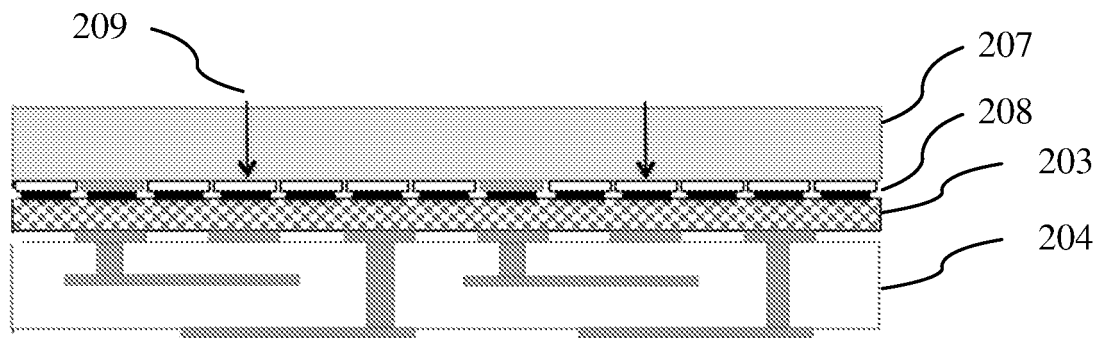


FIG. 4E

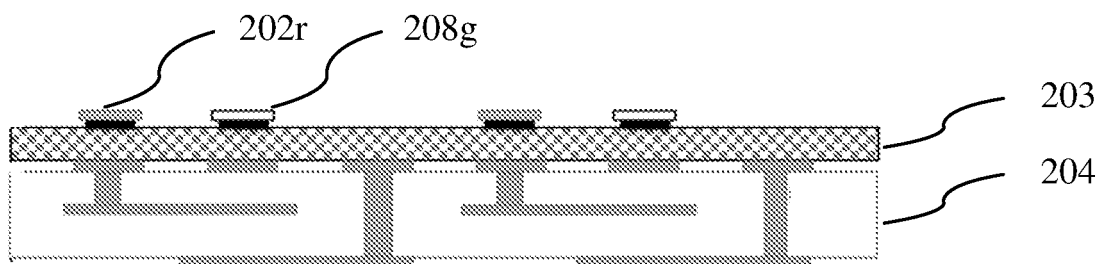


FIG. 4F

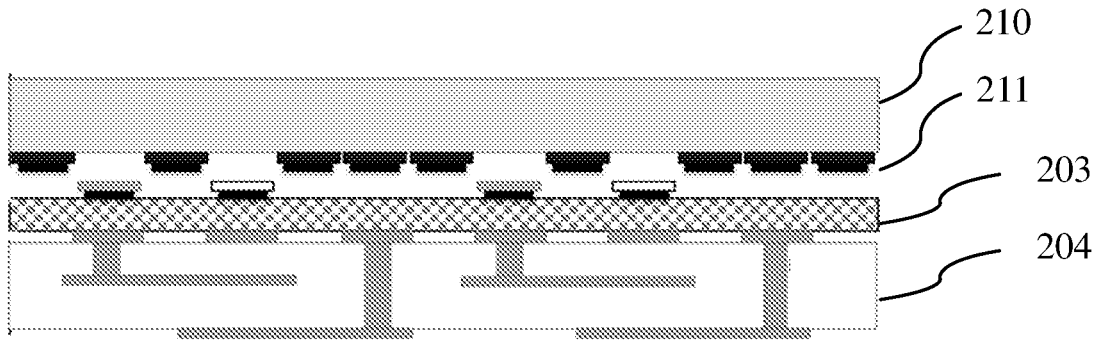


FIG. 4G

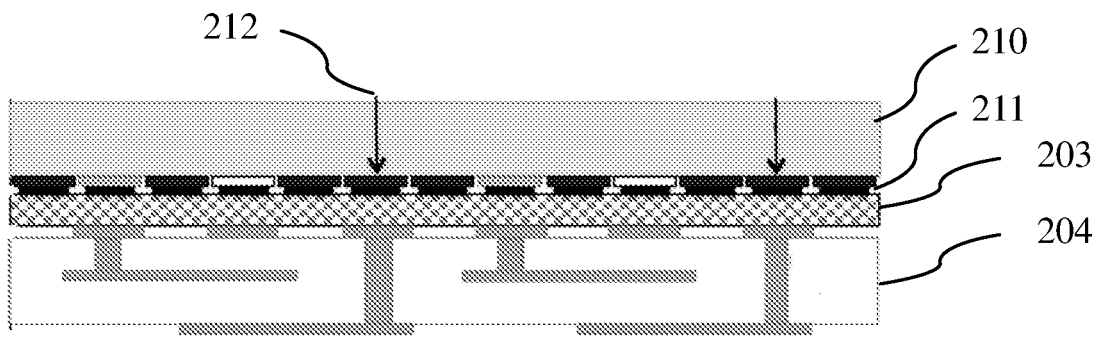


FIG. 4H

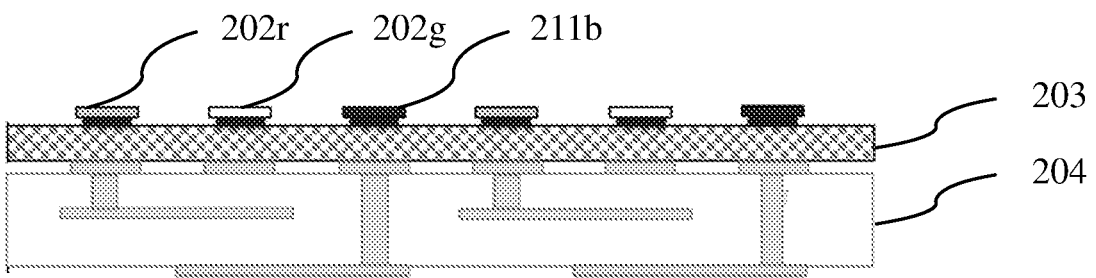


FIG. 4I

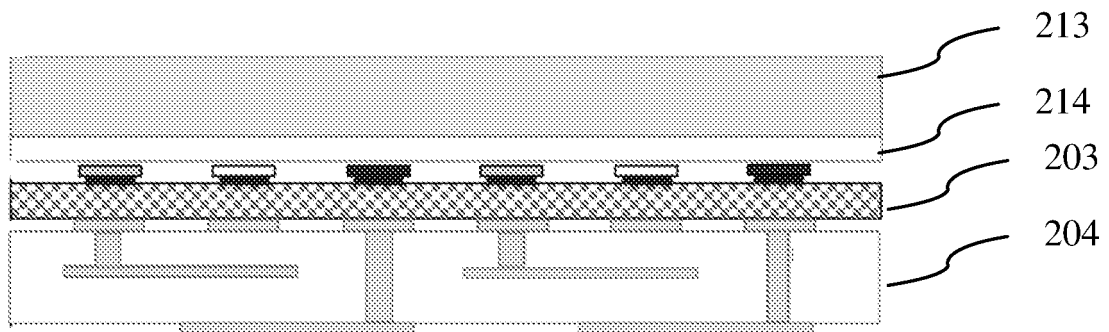


FIG. 4J

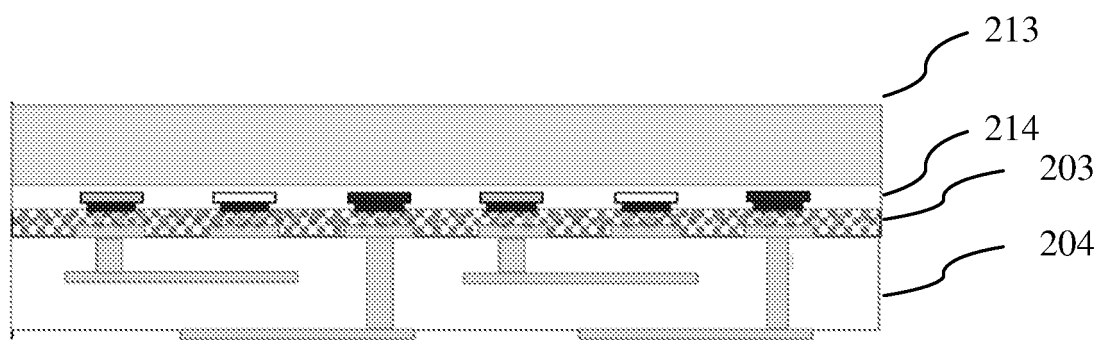


FIG. 4K

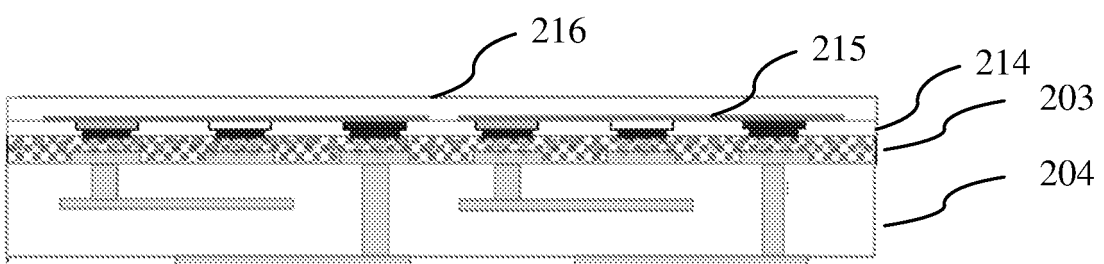
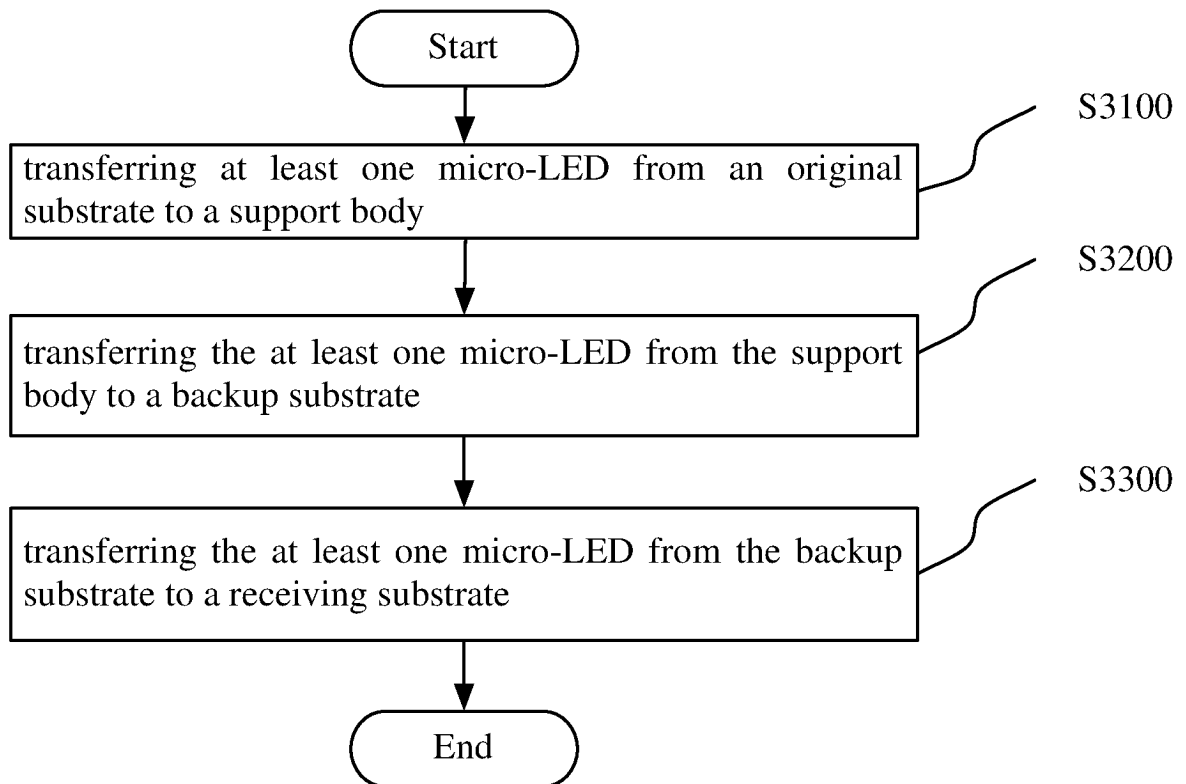
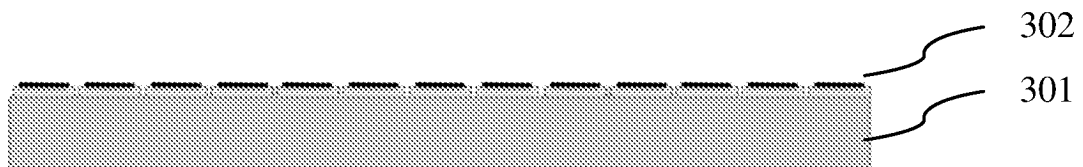


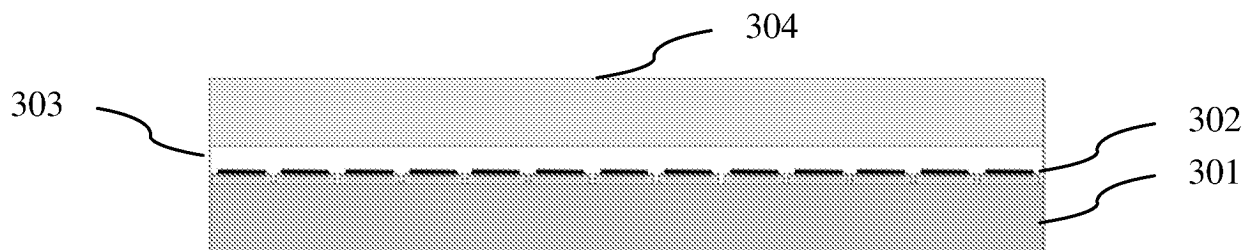
FIG. 4L



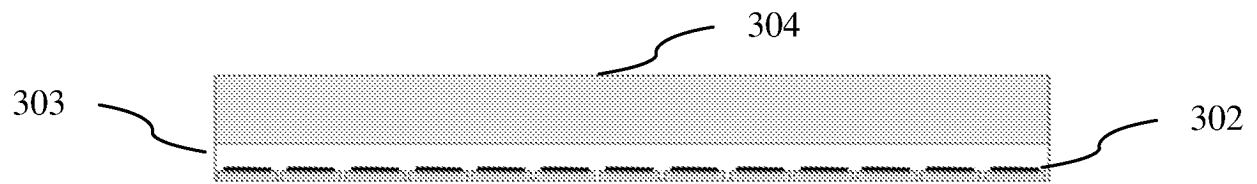
**FIG. 5**



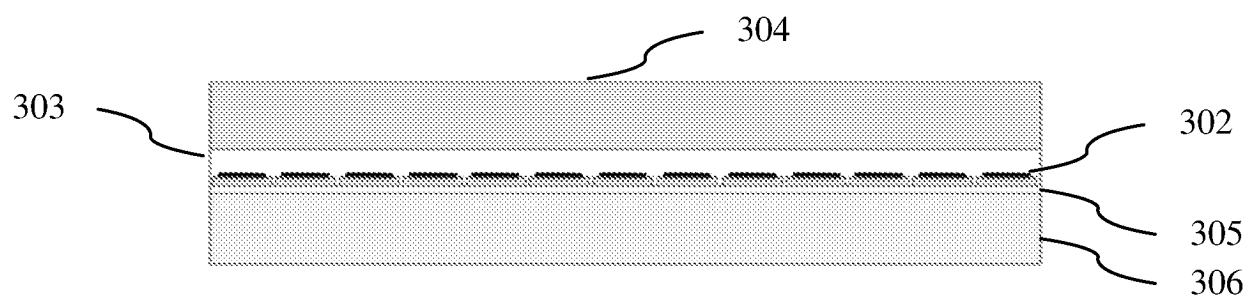
**FIG. 6A**



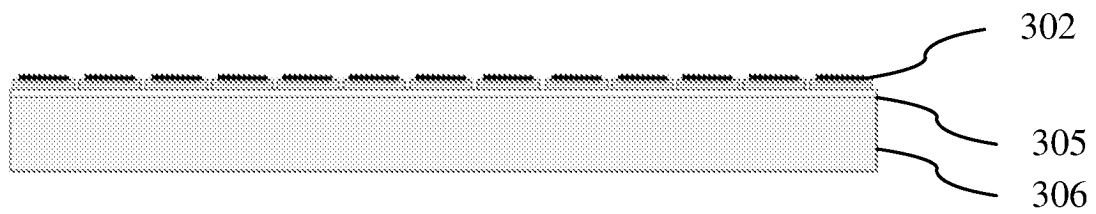
**FIG. 6B**



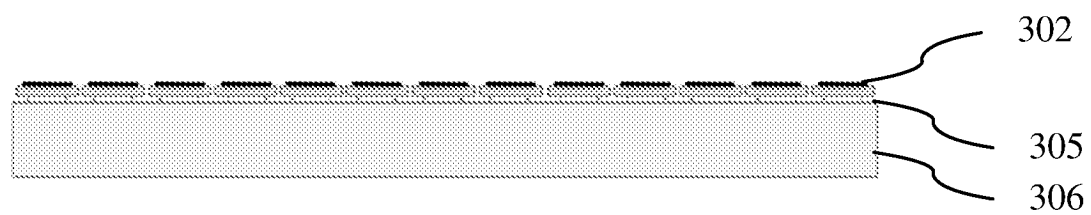
**FIG. 6C**



**FIG. 6D**



**FIG. 6E**



**FIG. 6F**



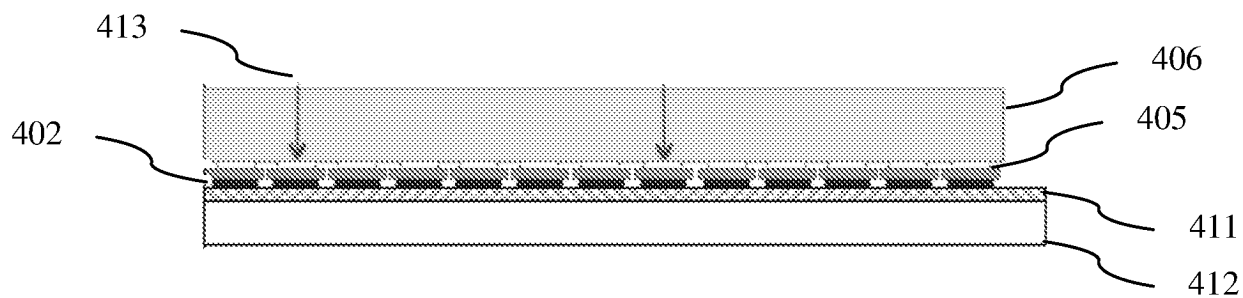


FIG. 7A

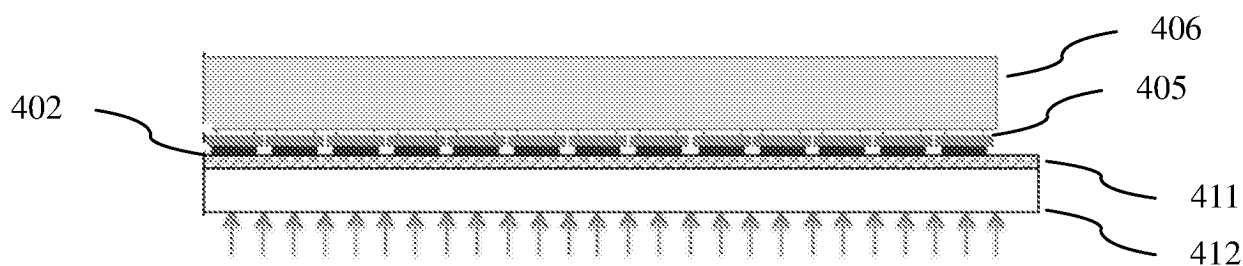


FIG. 7B

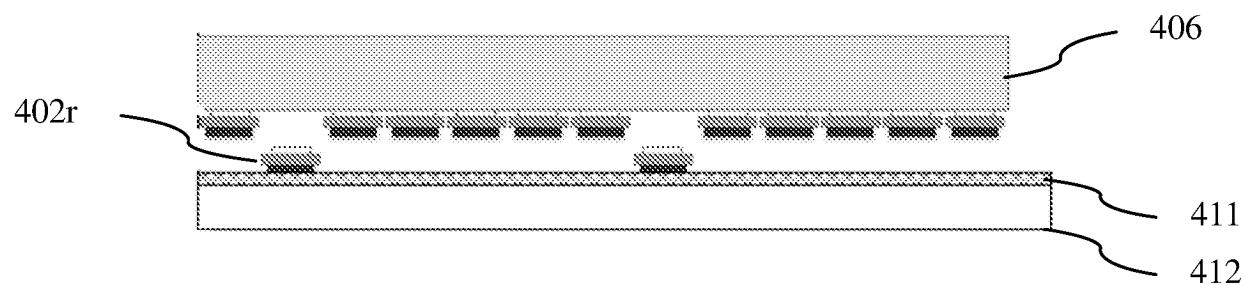


FIG. 7C

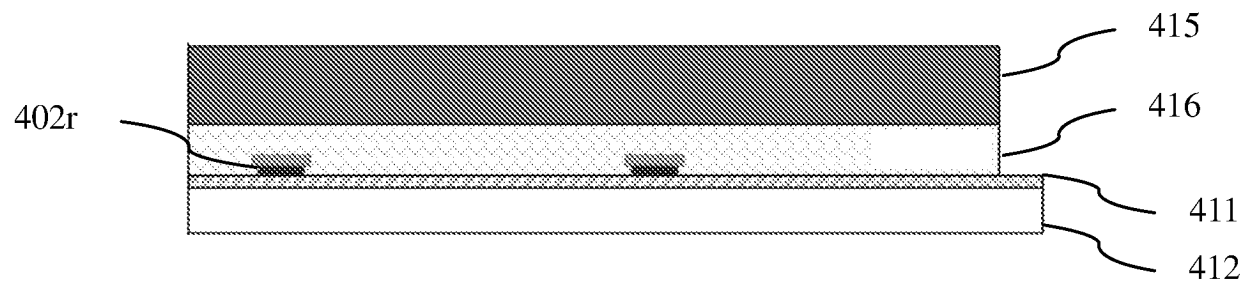


FIG. 7D

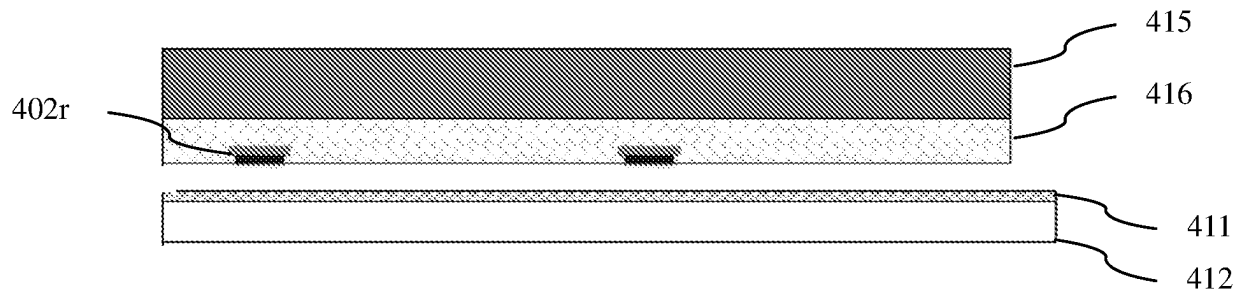


FIG. 7E

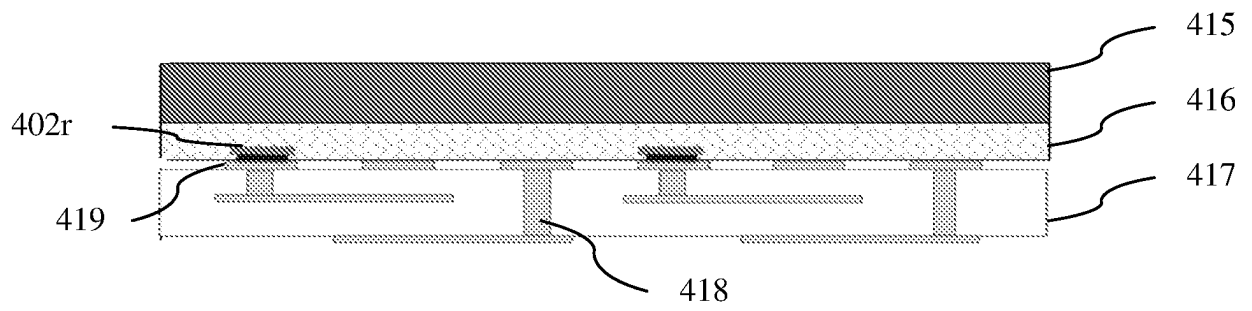


FIG. 7F

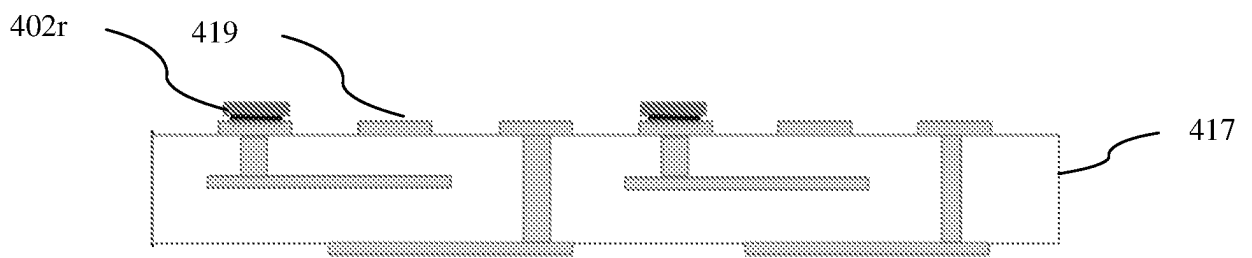


FIG. 7G

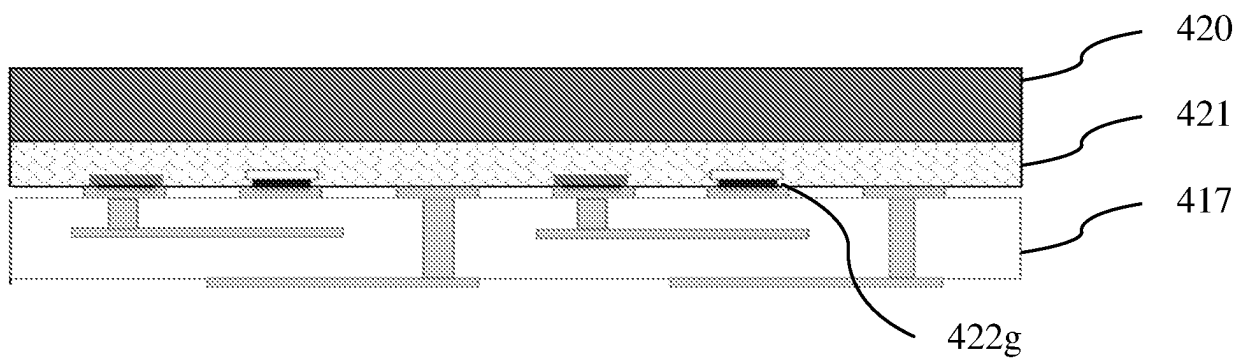
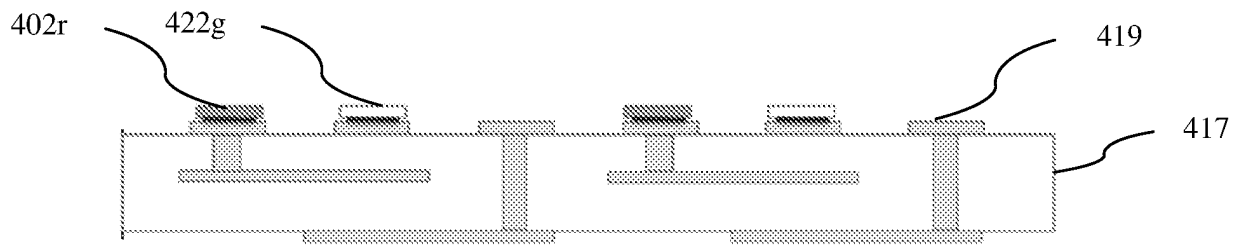
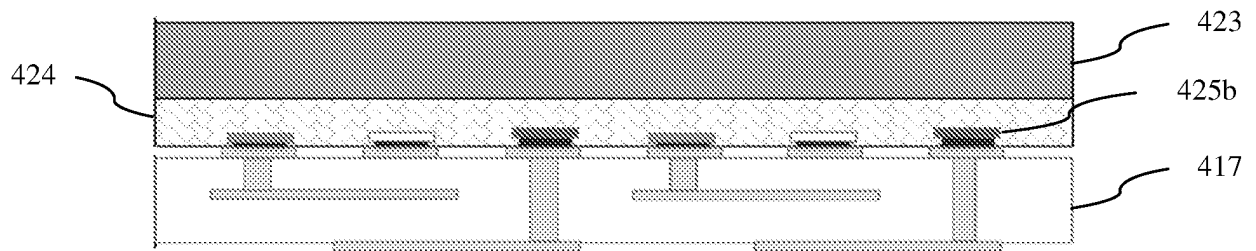


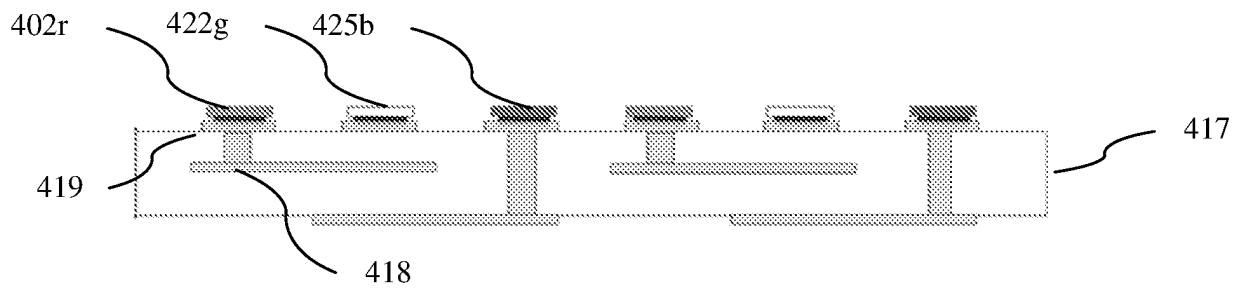
FIG. 7H



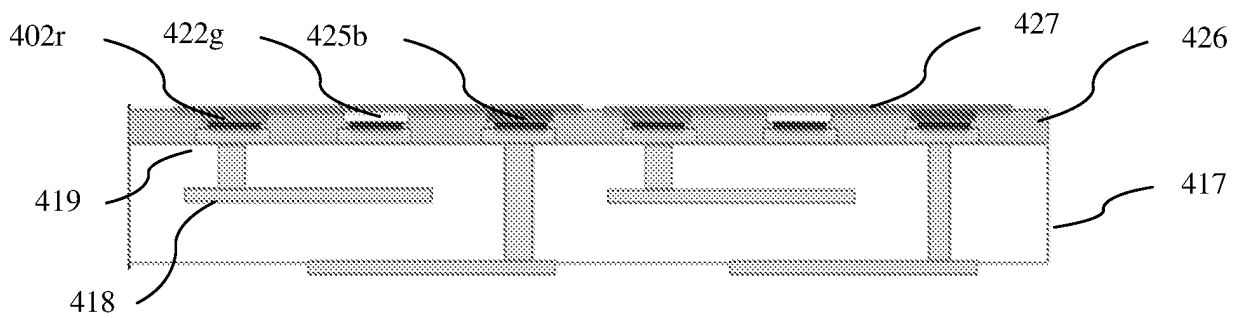
**FIG. 7I**



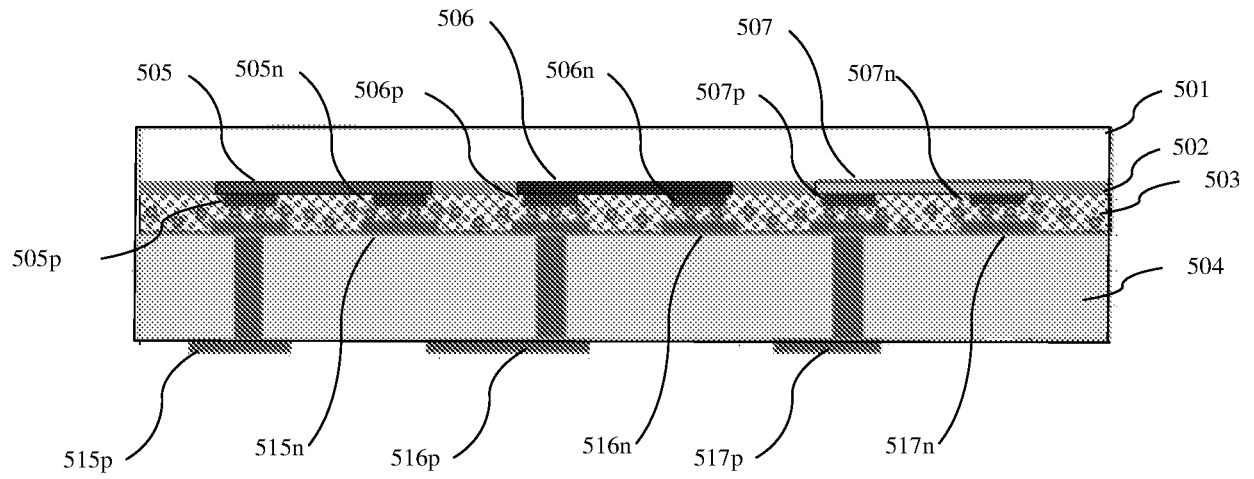
**FIG. 7J**



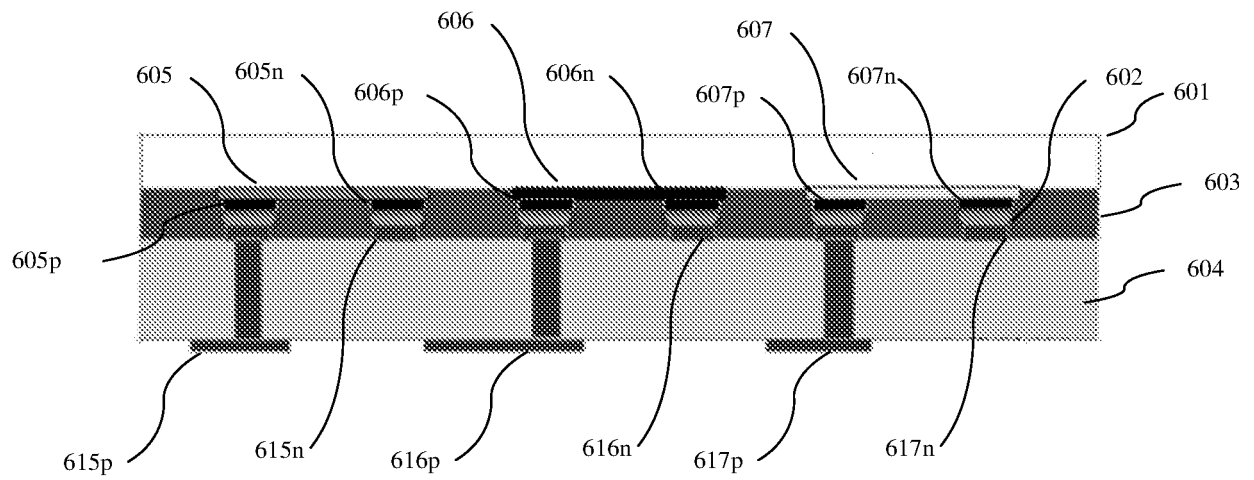
**FIG. 7K**



**FIG. 7L**



**FIG. 8**



**FIG. 9**

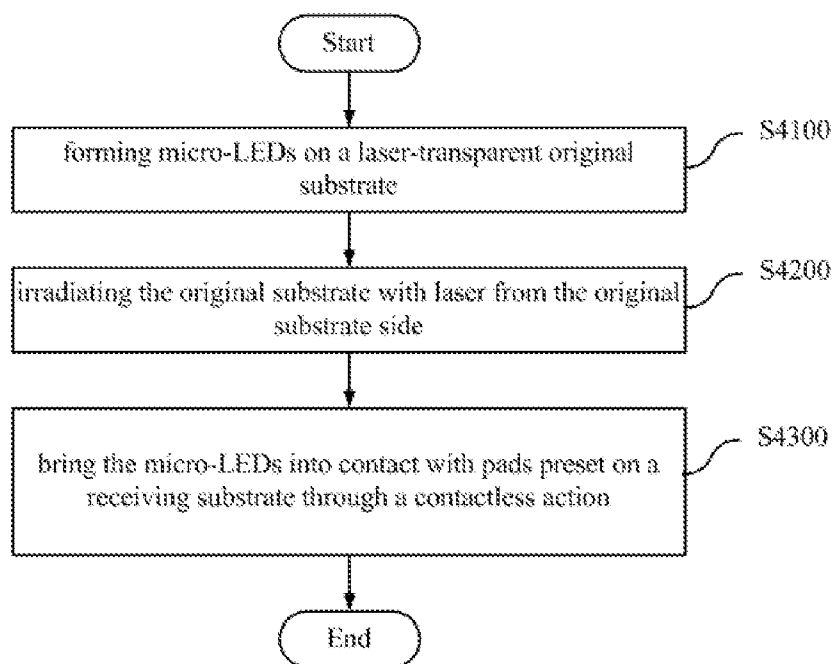


FIG. 10

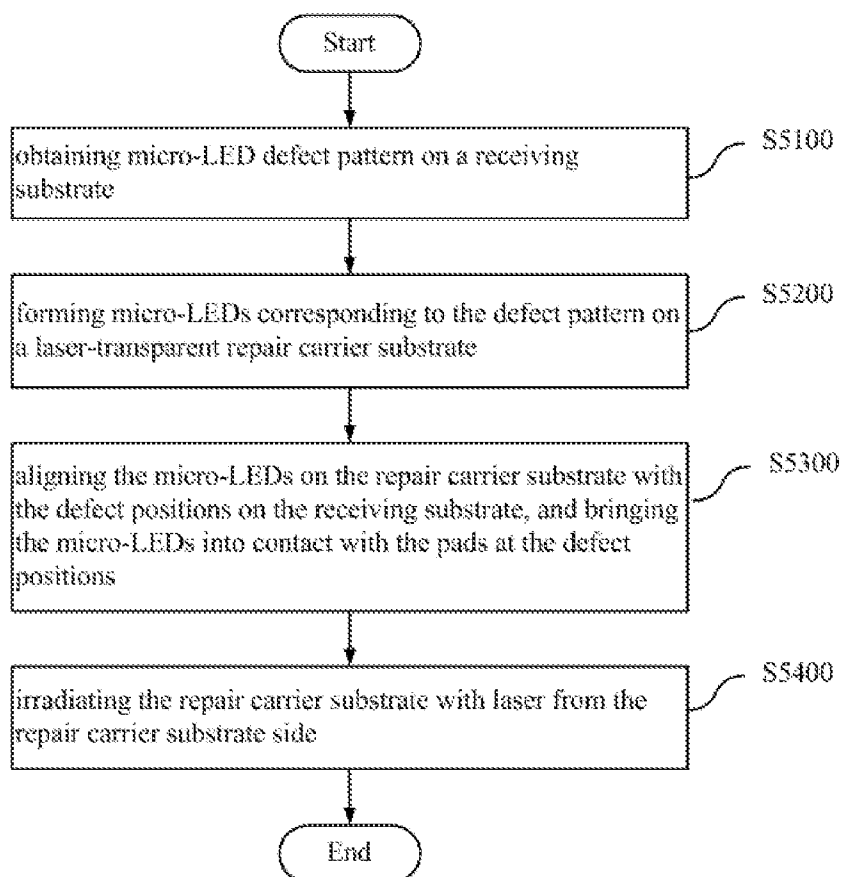
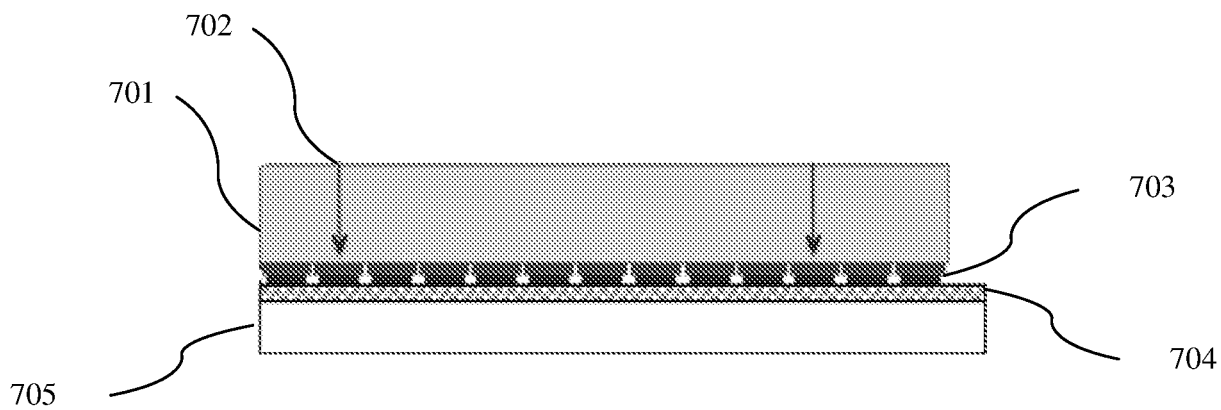
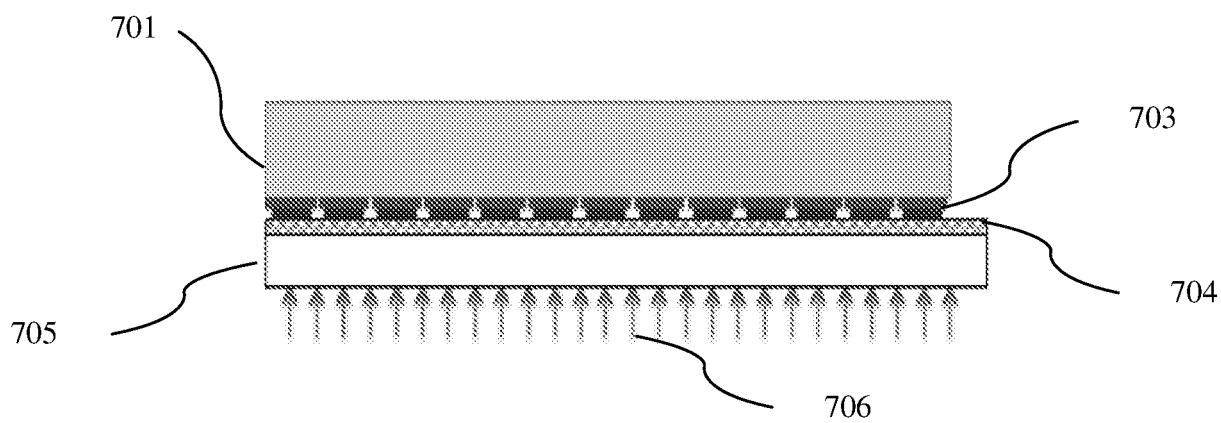


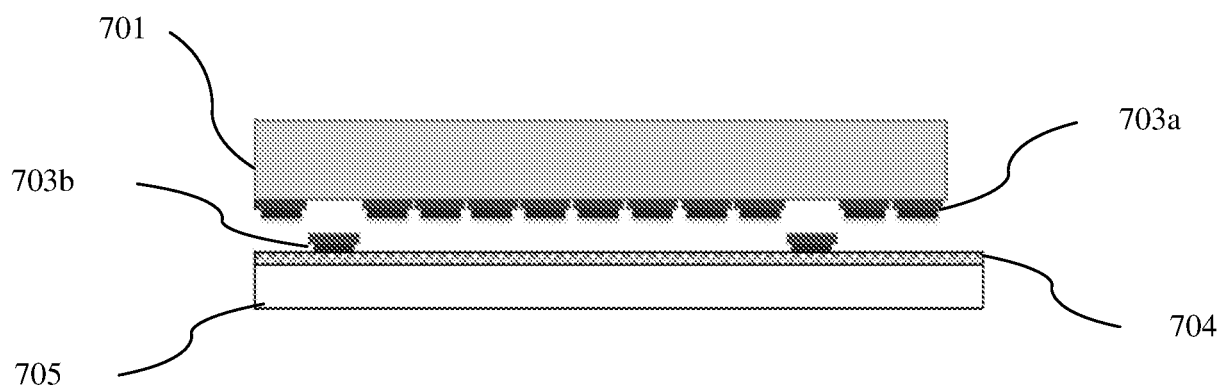
FIG. 11



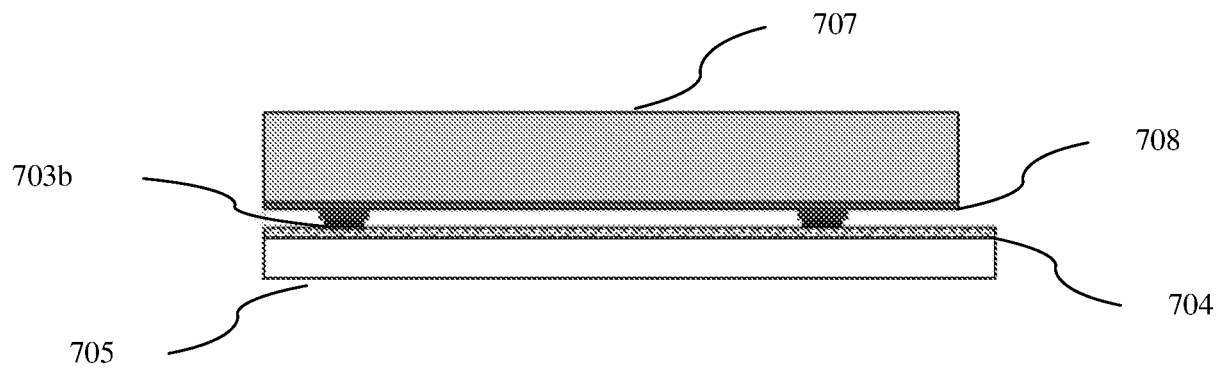
**FIG. 12A**



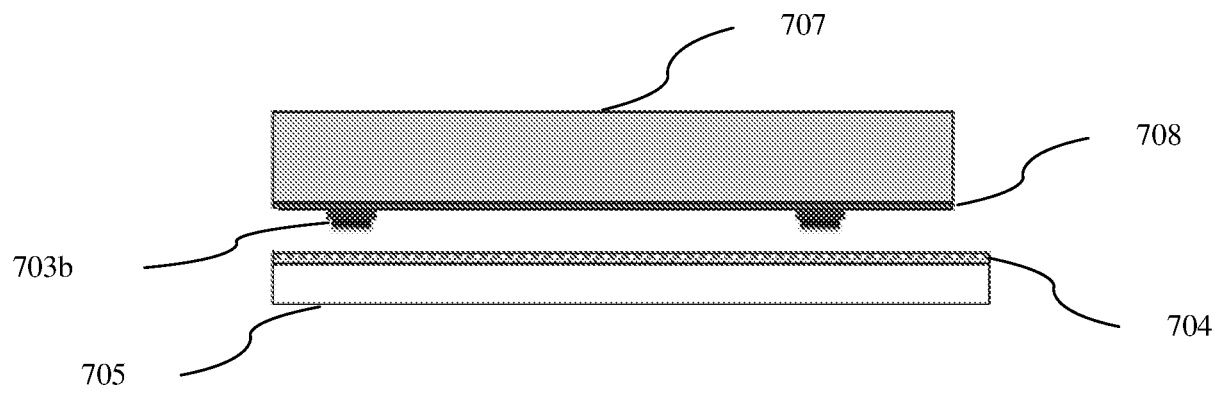
**FIG. 12B**



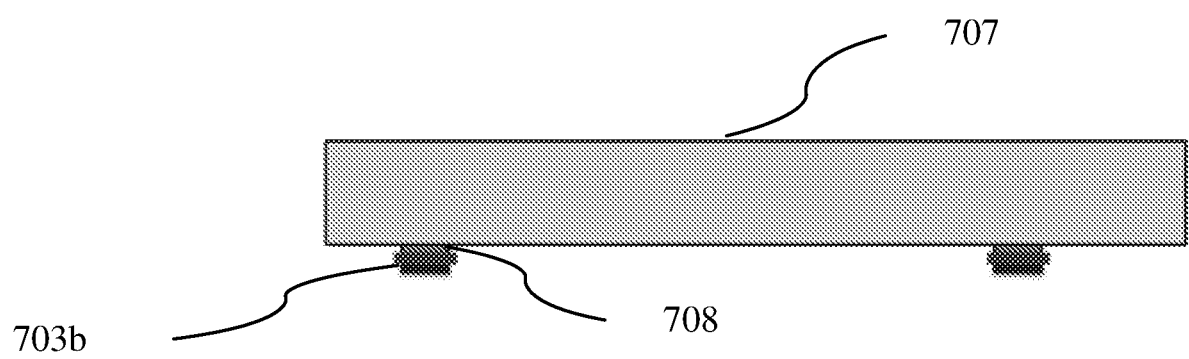
**FIG. 12C**



**FIG. 12D**



**FIG. 12E**



**FIG. 12F**

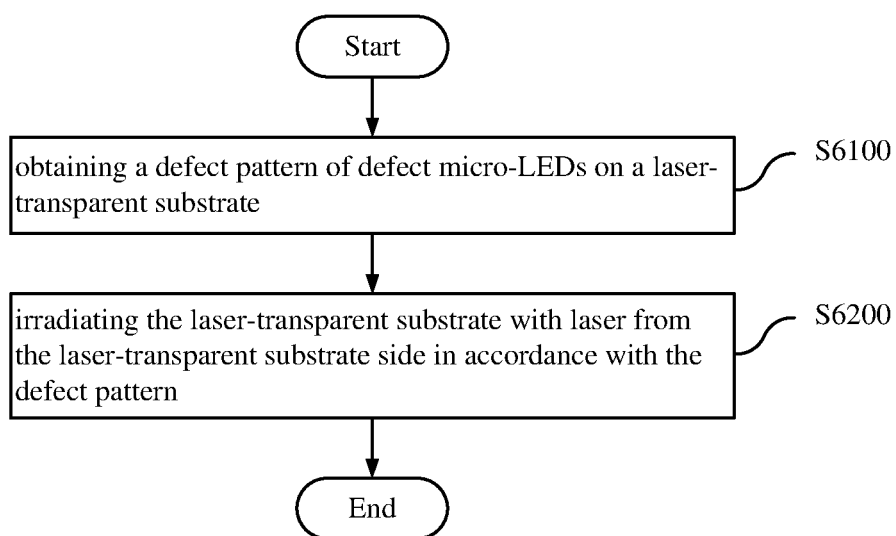


FIG. 13

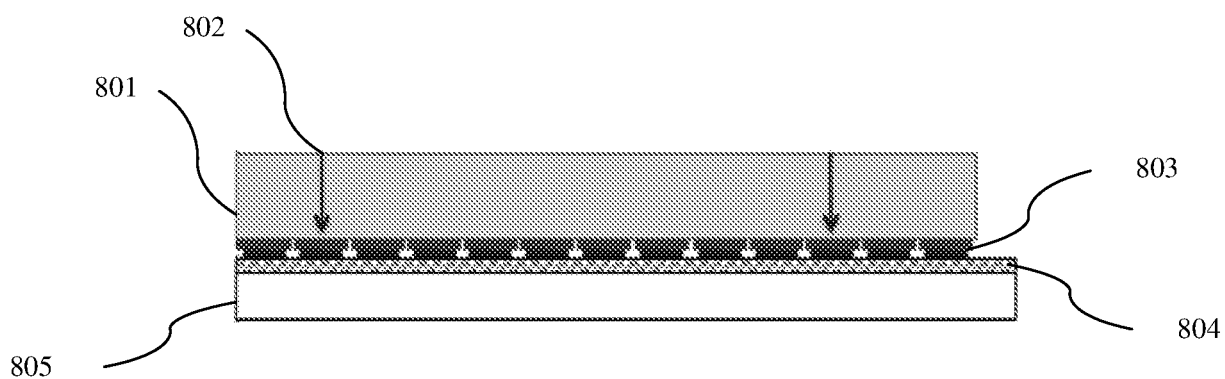


FIG. 14A

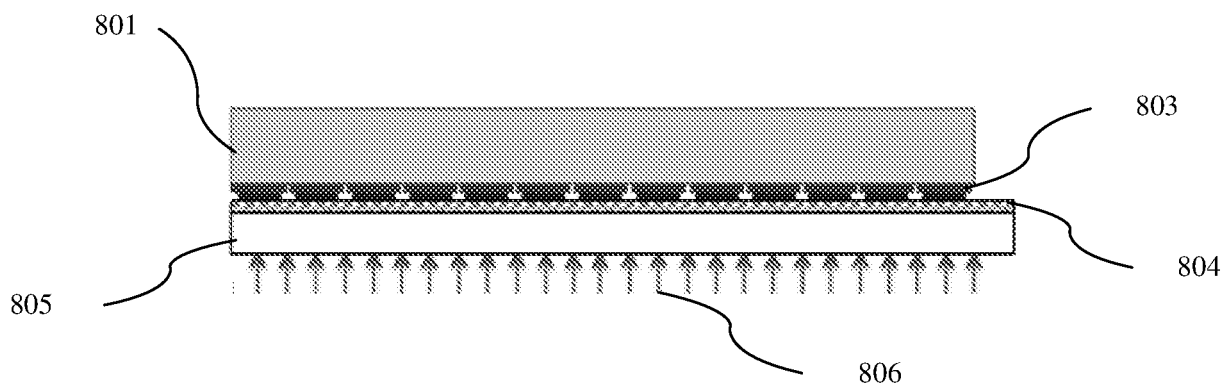
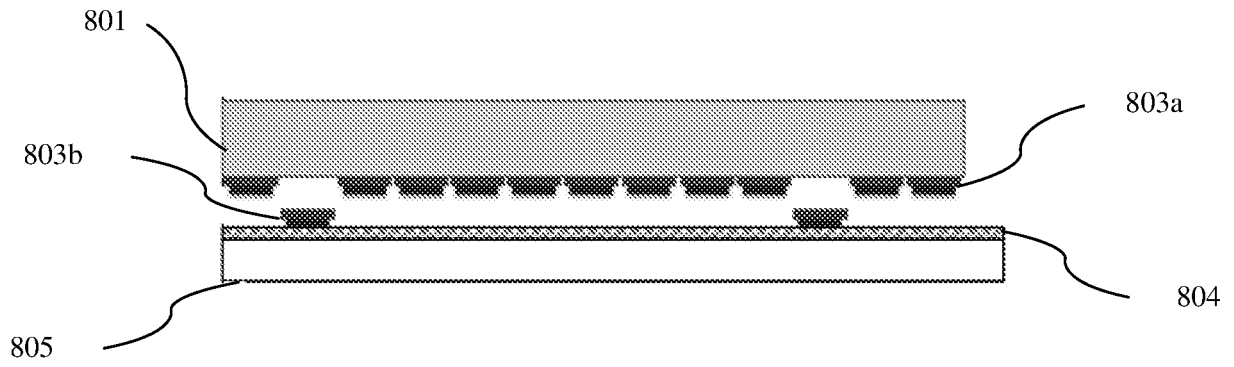
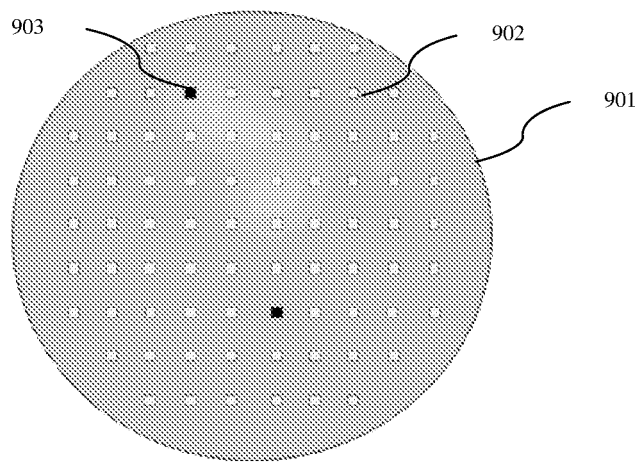


FIG. 14B

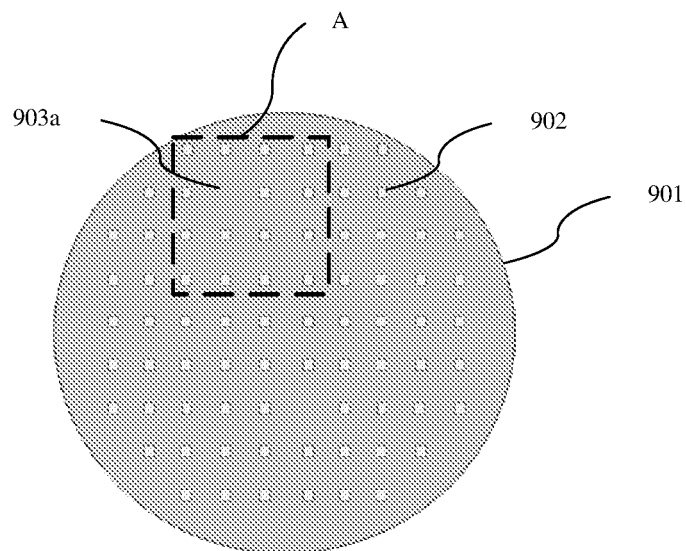




**FIG. 14C**



**FIG. 15A**



**FIG. 15B**

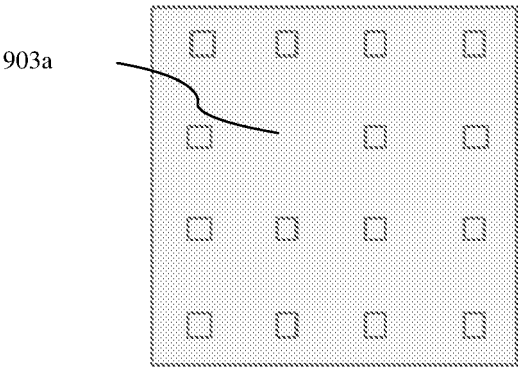


FIG. 16A

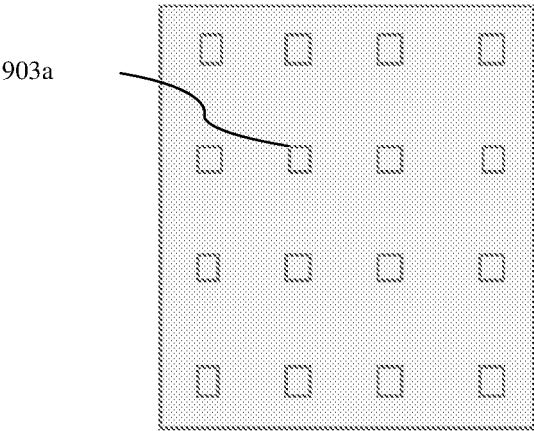


FIG. 16B

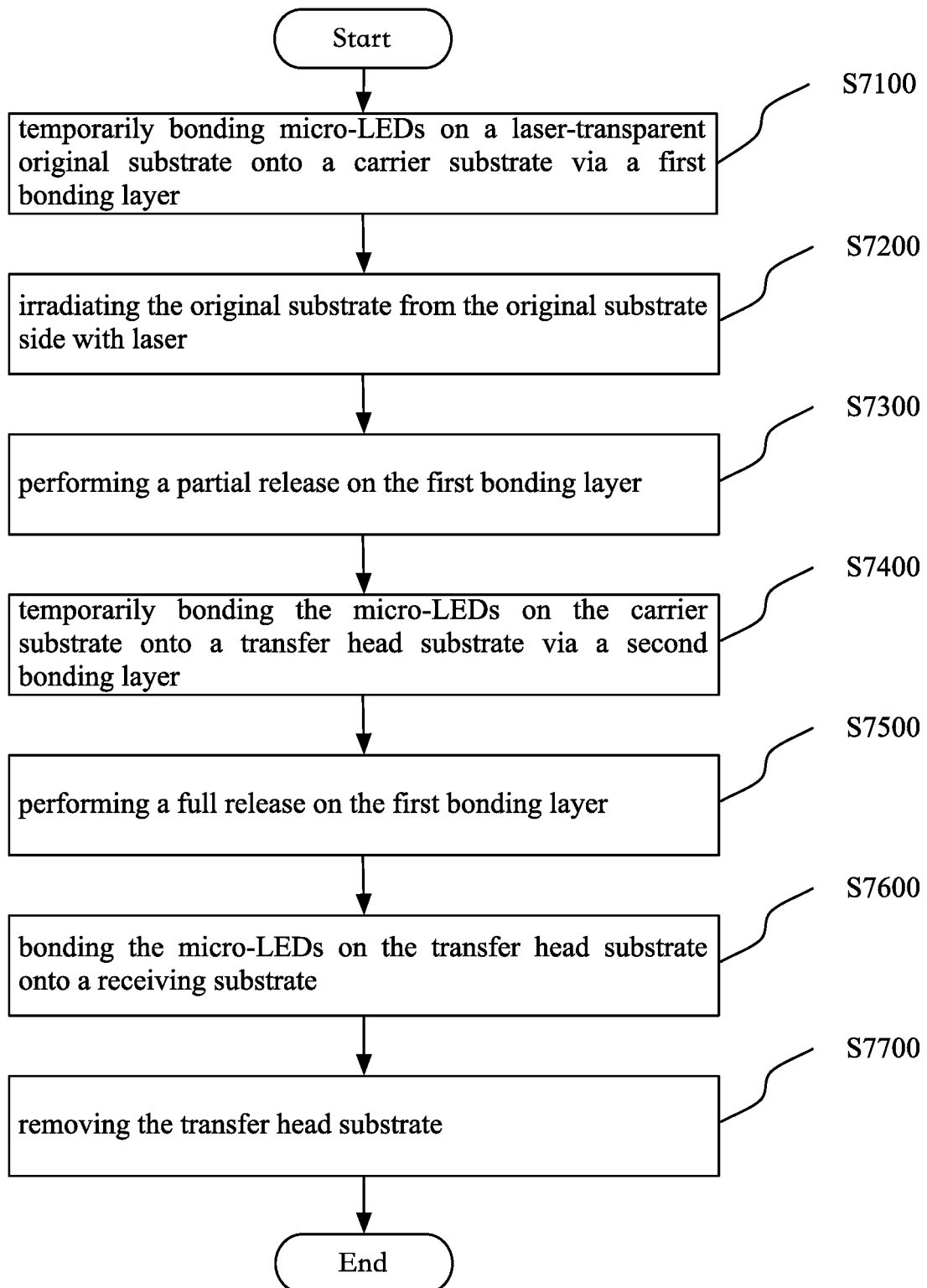
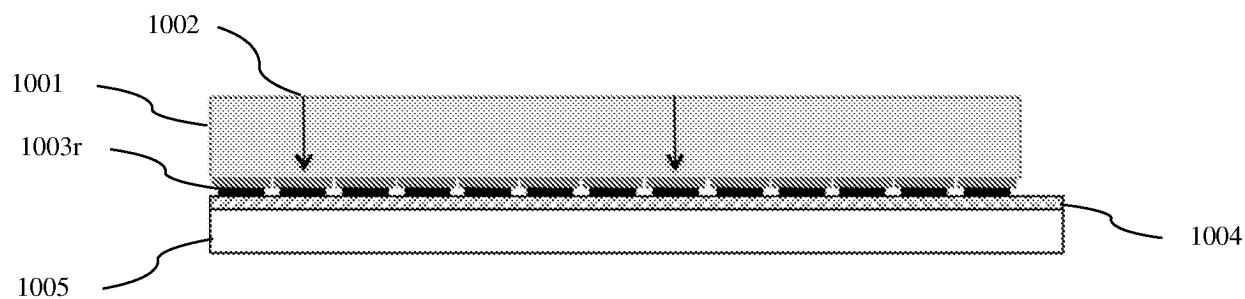
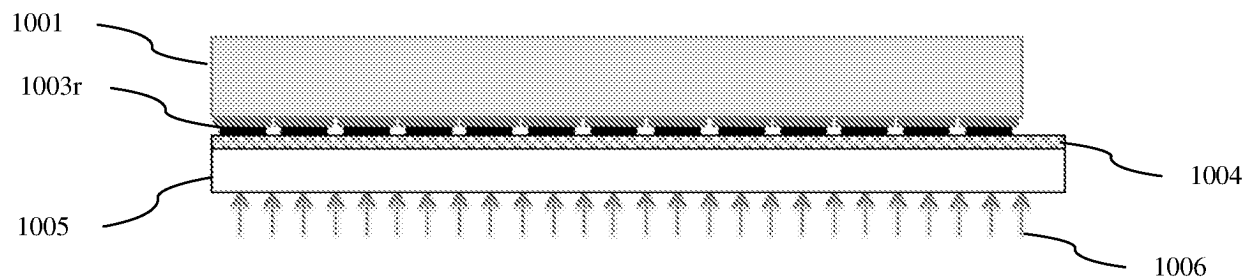


FIG. 17



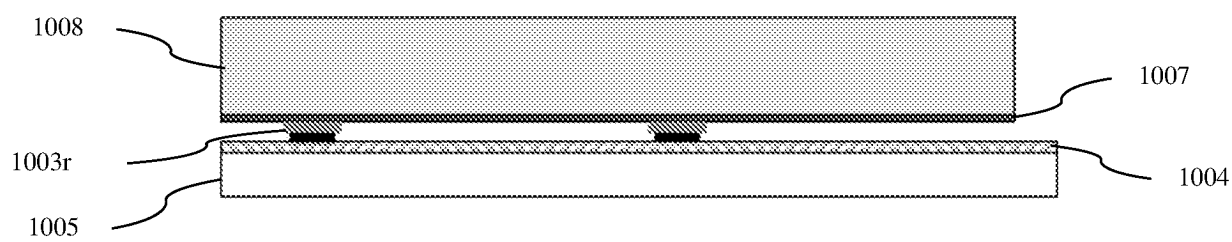
**FIG. 18A**



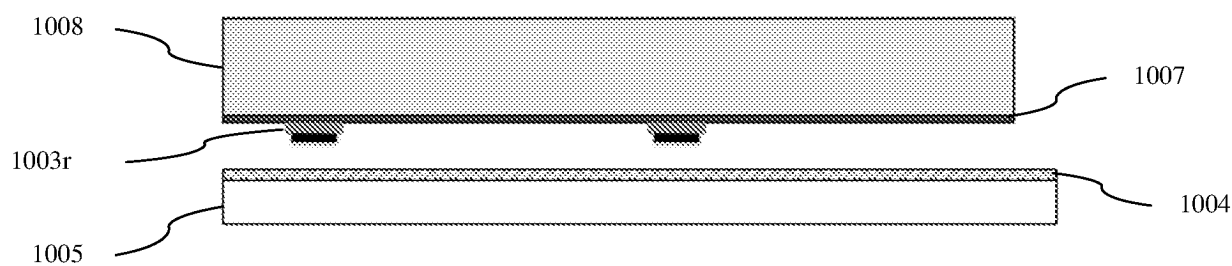
**FIG. 18B**



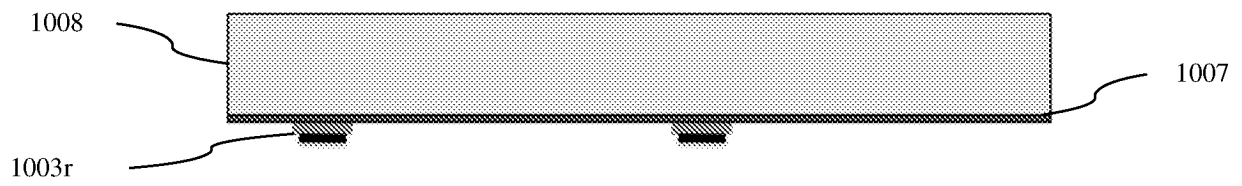
**FIG. 18C**



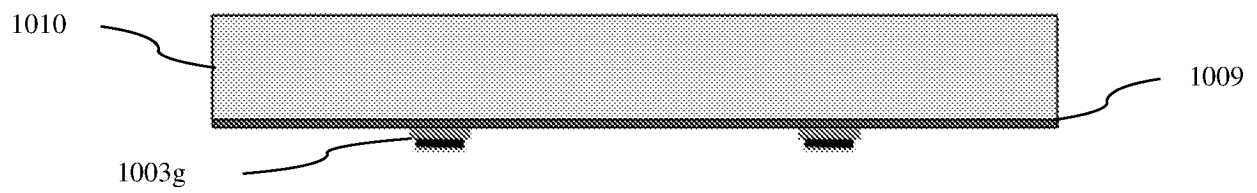
**FIG. 18D**



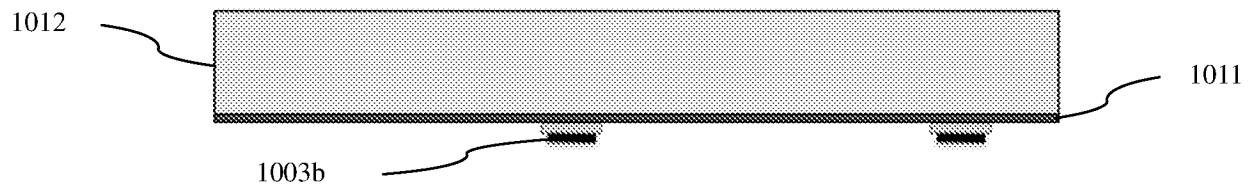
**FIG. 18E**



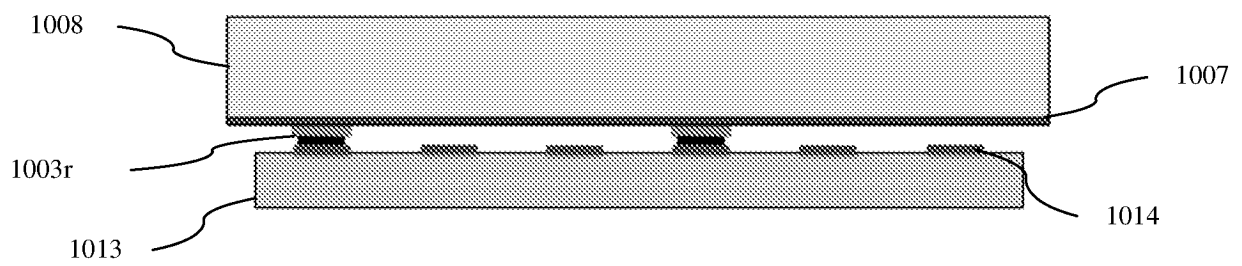
**FIG. 18F**



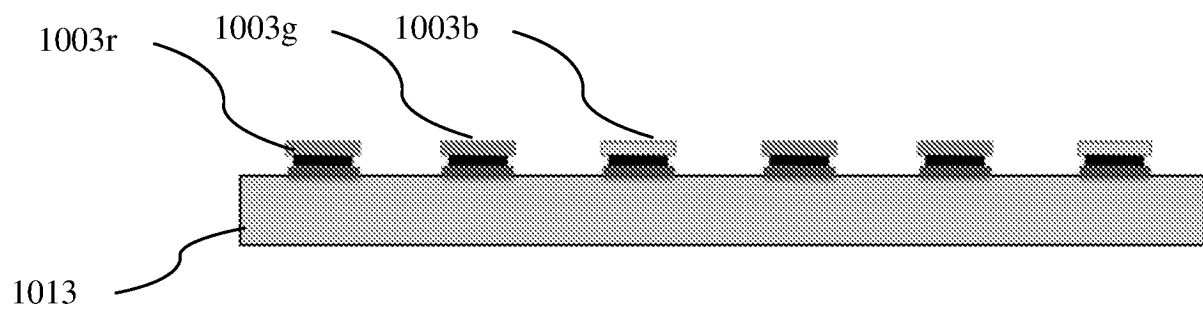
**FIG. 18G**



**FIG. 18H**



**FIG. 18I**



**FIG. 18J**

**REFERENCES CITED IN THE DESCRIPTION**

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**Patent documents cited in the description**

- US 8333860 B1 [0005]
- US 8426227 B1 [0006]
- US 20140159065 A1 [0007]
- US 20100259164 A1 [0007]
- US 20110151602 A1 [0007]

专利名称(译)	传输微LED的方法和制造微LED器件的方法		
公开(公告)号	<a href="#">EP3262694B1</a>	公开(公告)日	2019-08-21
申请号	EP2015906439	申请日	2015-10-20
[标]申请(专利权)人(译)	歌尔声学股份有限公司		
申请(专利权)人(译)	歌尔声学. INC		
当前申请(专利权)人(译)	歌尔声学. INC		
[标]发明人	ZOU QUANBO WANG ZHE		
发明人	ZOU, QUANBO WANG, ZHE		
IPC分类号	H01L33/00 H01L25/075		
CPC分类号	B32B37/025 H01L21/48 H01L24/75 H01L24/83 H01L24/97 H01L33/0093 H01L2224/7598 H01L2224/83 H01L2224/83005 H01L2224/97 H01L2924/12041 H01L21/6835 H01L22/20 H01L24/16 H01L24/81 H01L24/95 H01L25/0753 H01L2221/68322 H01L2221/68368 H01L2221/68381 H01L2224/131 H01L2224/16225 H01L2224/16238 H01L2224/81005 H01L2224/81024 H01L2224/81191 H01L2224/81815 H01L2224/8191 H01L2224/83851 H01L2224/95 H01L2224/95001 H01L2224/95136 H01L2224/81 H01L2924/00014 H01L2924/014 B81C3/001 H01L21/673 H01L21/67781		
其他公开文献	EP3262694A1 EP3262694A4		
外部链接	<a href="#">Espacenet</a>		

# 摘要(译)

本发明公开了一种微型LED的转移方法，制造方法，装置和电子设备。在晶圆级转移微LED的方法包括：通过第一粘接层将激光透明原始基板上的微LED暂时粘接到载体基板上；用激光照射原始基板，剥离选定的微型LED；在第一粘合层上进行部分剥离，将所选择的微LED转移到载体基板上；通过第二粘合层将载体基板上的微LED暂时粘合到转移头基板上；在第一粘合层上执行完全释放，以将微LED转移到转移头基板；将转移头基板上的微LED接合到接收基板上；通过释放第二粘合层去除转移头基板，以将微LED转移到接收基板。

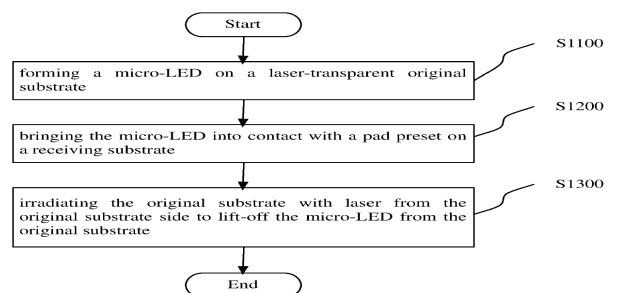


FIG. 1

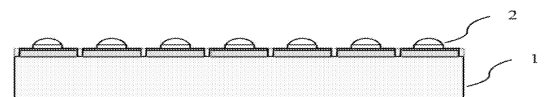


FIG. 2A